LPDDR4 SDRAM

MT53B128M32

Features

- Ultra-low-voltage core and I/O power supplies
  - V_{DD1} = 1.70–1.95V; 1.8V nominal
  - V_{DD2}/V_{DDQ} = 1.06–1.17V; 1.10V nominal
- Frequency range
  - 1600–10 MHz (data rate range: 3200–20 Mb/s/pin)
- 16*n* prefetch DDR architecture
- 2-channel partitioned architecture for low RD/WR energy and low average latency
- 8 internal banks per channel for concurrent operation
- Single-data-rate CMD/ADR entry
- Bidirectional/differential data strobe per byte lane
- Programmable READ and WRITE latencies (RL/WL)
- Programmable and on-the-fly burst lengths (BL = 16, 32)
- Directed per-bank refresh for concurrent bank operation and ease of command scheduling
- Up to 12.8 GB/s per die (2 channels x 6.4 GB/s)
- On-chip temperature sensor to control self refresh rate
- Partial-array self refresh (PASR)
- Selectable output drive strength (DS)
- Clock-stop capability
- RoHS-compliant, "green" packaging
- Programmable V_{SSQ} (ODT) termination

Options	Marking
• V_{DD1}/V_{DD2}: 1.8V/1.1V	B
• Array configuration	
– 128 Meg x 32 (2 - x16 channels)	128M32
• Device configuration	
– 1 x 128M32 die in package	D1
• FBGA "green" package	
– 200-ball VFBGA (10mm x 14.5mm), Ø0.35 SMD	DT
– 200-ball WFBGA (10mm x 14.5mm), Ø0.28 SMD	NP
– 200-ball WFBGA (10mm x 14.5mm), Ø0.35 SMD	DS
• Speed grade, cycle time	
– 535ps @ RL = 32/36	-053
– 625ps @ RL = 28/32	-062
• Special option	
– standard	–
• Operating temperature range	
– –30°C to +85°C	WT
– –40°C to +95°C	IT
• Revision	:A

Table 1: Key Timing Parameters

Speed Grade	Clock Rate (MHz)	Data Rate (Mb/s/pin)	WRITE Latency Set A	WRITE Latency Set B	READ Latency (DBI Disabled)	READ Latency (DBI Enabled)
-053	1866	3733	16	30	32	36
-062	1600	3200	14	26	28	32

SDRAM Addressing

The table below shows addressing for the 4Gb die density. Where applicable, a distinction is made between per-channel and per-die parameters. All bank, row, and column addresses are shown per-channel.

Table 2: Device Addressing

Configuration		**128M32 (4Gb)**
Die per package		**1**
Device density (per die)		**4Gb**
Device density (per channel)		**2Gb**
Configuration		16Mb x 16 DQ x 8 banks x 2 channels x 1 rank
Number of channels (per die)		2
Number of ranks per channel		1
Number of banks (per channel)		8
Array prefetch (bits) (per channel)		256
Number of rows (per bank)		16,384
Number of columns (fetch boundaries)		64
Page size (bytes)		2048
Channel density (bits per channel)		2,147,483,648
Total density (bits per die)		4,294,967,296
Bank address		BA[2:0]
x16	Row addresses	R[13:0]
	Column addresses	C[9:0]
Burst starting address boundary		64-bit

Notes: 1. The lower two column addresses (C0–C1) are assumed to be zero and are not transmitted on the CA bus.
2. Row and column address values on the CA bus that are not used for a particular density are "Don't Care."
3. For non-binary memory densities, only half of the row address space is valid. When the MSB address bit is HIGH, the MSB - 1 address bit must be LOW.

Part Number and Part Marking Information

Figure 1: Part Number Chart

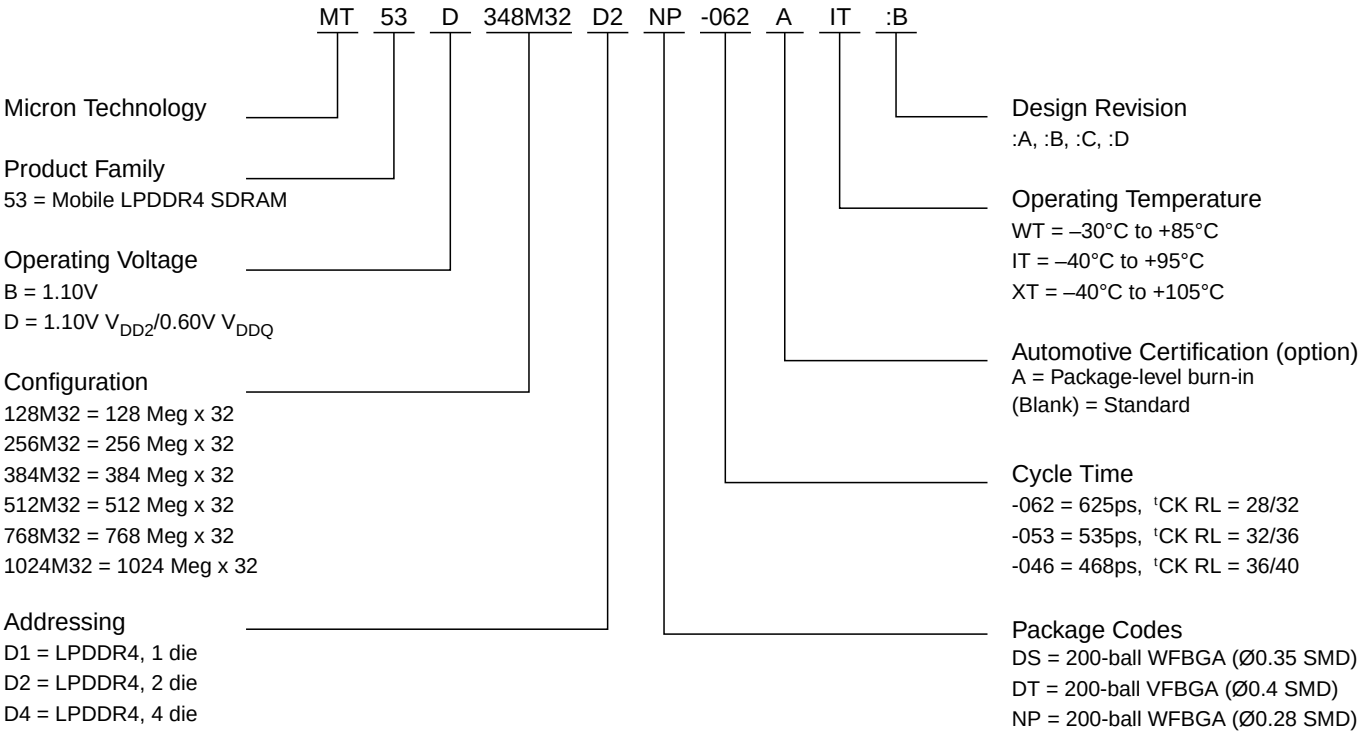

Table 3: Part Number List

Part Number	Total Density	Data Rate per Pin
MT53B128M32D1DT-053 IT:A	512MB (4Gb)	3733 Mb/s
MT53B128M32D1DS-062 IT:A	512MB (4Gb)	3200 Mb/s
MT53B128M32D1DS-062 WT:A	512MB (4Gb)	3200 Mb/s
MT53B128M32D1NP-062 IT:A	512MB (4Gb)	3200 Mb/s
MT53B128M32D1NP-062 WT:A	512MB (4Gb)	3200 Mb/s

FBGA Part Marking Decoder

Due to space limitations, FBGA-packaged components have an abbreviated part marking that is different from the part number. Micron's FBGA part marking decoder is available at www.micron.com/decoder.

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General Description

The 4Gb Mobile Low-Power DDR4 SDRAM (LPDDR4) is a high-speed CMOS, dynamic random-access memory. The device is internally configured with 2 x16 channels, each channel having 8-banks.

Each of the x16's 268,435,456-bit banks is organized as 16,384 rows by 1024 columns by 16 bits.

General Notes

Throughout the data sheet, figures and text refer to DQs as "DQ." DQ should be interpreted as any or all DQ collectively, unless specifically stated otherwise.

"DQS" and "CK" should be interpreted as DQS_t, DQS_c and CK_t, CK_c respectively, unless specifically stated otherwise. "CA" includes all CA pins used for a given density.

In timing diagrams, "CMD" is used as an indicator only. Actual signals occur on CA[5:0].

V_{REF} indicates V_{REFCA} and V_{REFDQ}.

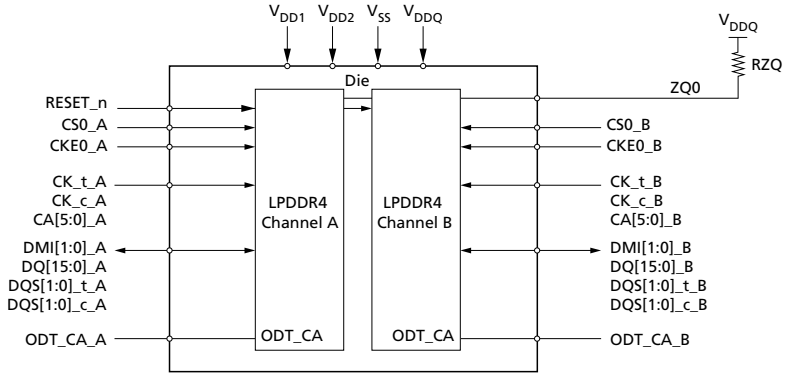
Complete functionality may be described throughout the entire document. Any page or diagram may have been simplified to convey a topic and may not be inclusive of all requirements.

Any specific requirement takes precedence over a general statement.

Any functionality not specifically stated herein is considered undefined, illegal, is not supported, and will result in unknown operation.

Package Block Diagrams

Figure 2: Single-Die, Dual-Channel, Single-Rank Package Block Diagram



Ball Assignments and Descriptions

Figure 3: 200-Ball Dual-Channel, Single-Rank Discrete FBGA

	1	2	3	4	5	6	7	8	9	10	11	12
A	DNU	DNU	V_{SS}	V_{DD2}	ZQ0			NC	V_{DD2}	V_{SS}	DNU	DNU
B	DNU	DQ0_A	V_{DDQ}	DQ7_A	V_{DDQ}			V_{DDQ}	DQ15_A	V_{DDQ}	DQ8_A	DNU
C	V_{SS}	DQ1_A	DMI0_A	DQ6_A	V_{SS}			V_{SS}	DQ14_A	DMI1_A	DQ9_A	V_{SS}
D	V_{DDQ}	V_{SS}	DQS0_t_A	V_{SS}	V_{DDQ}			V_{DDQ}	V_{SS}	DQS1_t_A	V_{SS}	V_{DDQ}
E	V_{SS}	DQ2_A	DQS0_c_A	DQ5_A	V_{SS}			V_{SS}	DQ13_A	DQS1_c_A	DQ10_A	V_{SS}
F	V_{DD1}	DQ3_A	V_{DDQ}	DQ4_A	V_{DD2}			V_{DD2}	DQ12_A	V_{DDQ}	DQ11_A	V_{DD1}
G	V_{SS}	ODT_CA_A	V_{SS}	V_{DD1}	V_{SS}			V_{SS}	V_{DD1}	V_{SS}	NC	V_{SS}
H	V_{DD2}	CA0_A	NC	CS0_A	V_{DD2}			V_{DD2}	CA2_A	CA3_A	CA4_A	V_{DD2}
J	V_{SS}	CA1_A	V_{SS}	CKE0_A	NC			CK_t_A	CK_c_A	V_{SS}	CA5_A	V_{SS}
K	V_{DD2}	V_{SS}	V_{DD2}	V_{SS}	NC			NC	V_{SS}	V_{DD2}	V_{SS}	V_{DD2}
L												
M												
N	V_{DD2}	V_{SS}	V_{DD2}	V_{SS}	NC			NC	V_{SS}	V_{DD2}	V_{SS}	V_{DD2}
P	V_{SS}	CA1_B	V_{SS}	CKE0_B	NC			CK_t_B	CK_c_B	V_{SS}	CA5_B	V_{SS}
R	V_{DD2}	CA0_B	NC	CS0_B	V_{DD2}			V_{DD2}	CA2_B	CA3_B	CA4_B	V_{DD2}
T	V_{SS}	ODT_CA_B	V_{SS}	V_{DD1}	V_{SS}			V_{SS}	V_{DD1}	V_{SS}	RESET_n	V_{SS}
U	V_{DD1}	DQ3_B	V_{DDQ}	DQ4_B	V_{DD2}			V_{DD2}	DQ12_B	V_{DDQ}	DQ11_B	V_{DD1}
V	V_{SS}	DQ2_B	DQS0_c_B	DQ5_B	V_{SS}			V_{SS}	DQ13_B	DQS1_c_B	DQ10_B	V_{SS}
W	V_{DDQ}	V_{SS}	DQS0_t_B	V_{SS}	V_{DDQ}			V_{DDQ}	V_{SS}	DQS1_t_B	V_{SS}	V_{DDQ}
Y	V_{SS}	DQ1_B	DMI0_B	DQ6_B	V_{SS}			V_{SS}	DQ14_B	DMI1_B	DQ9_B	V_{SS}
AA	DNU	DQ0_B	V_{DDQ}	DQ7_B	V_{DDQ}			V_{DDQ}	DQ15_B	V_{DDQ}	DQ8_B	DNU
AB	DNU	DNU	V_{SS}	V_{DD2}	V_{SS}			V_{SS}	V_{DD2}	V_{SS}	DNU	DNU
	1	2	3	4	5	6	7	8	9	10	11	12

Top View (ball down)

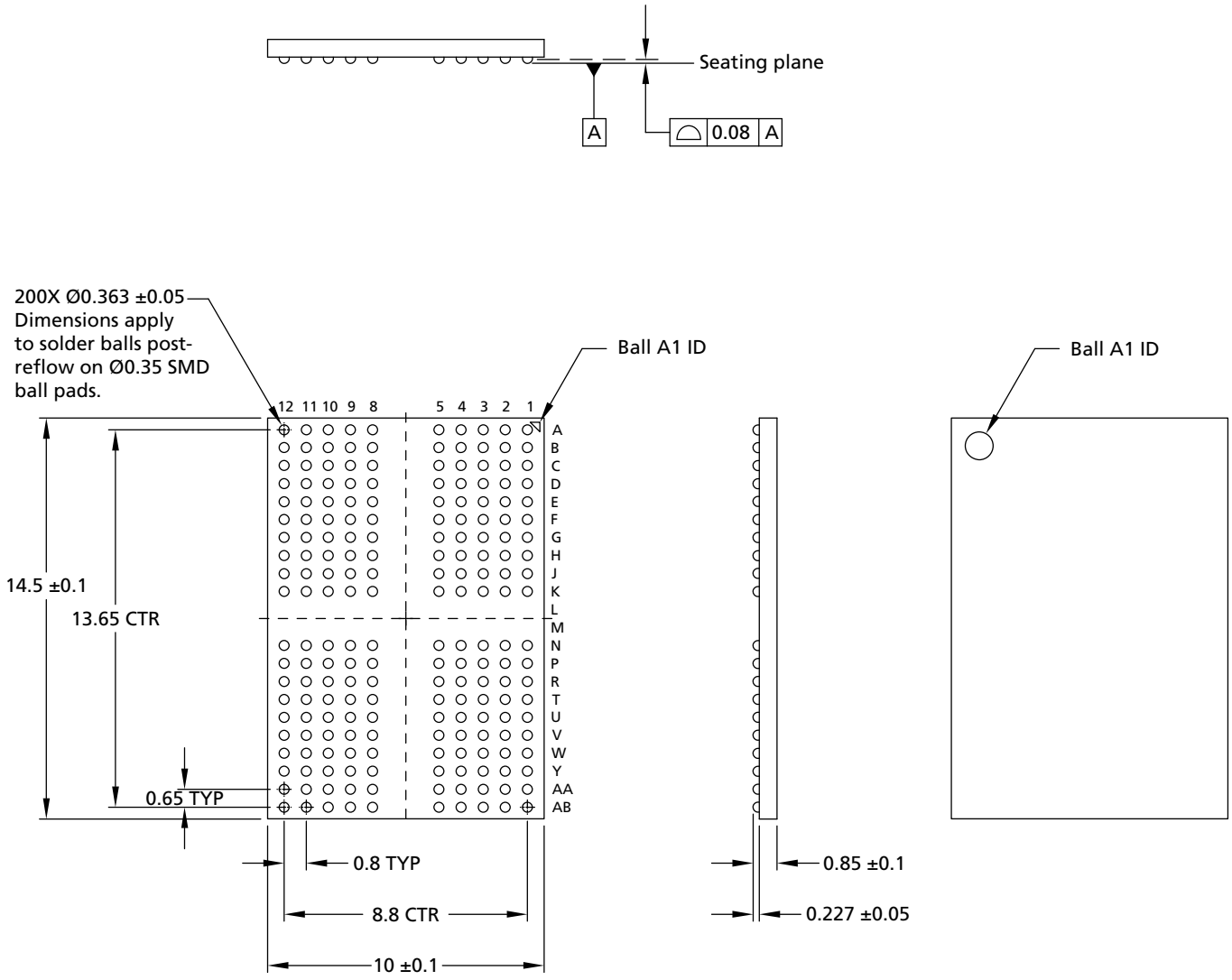
LPDDR4_A (Channel A) | LPDDR4_B (Channel B) | ZQ, ODT_CA, RESET | Supply | Ground

Table 4: Ball/Pad Descriptions

Symbol	Type	Description
CK_t_A, CK_c_A, CK_t_B, CK_c_B	Input	**Clock:** CK_t and CK_c are differential clock inputs. All address, command and control input signals are sampled on positive edge of CK_t and the negative edge of CK_c. AC timings for CA parameters are referenced to clock. Each channel (A, B) has its own clock pair.
CKE0_A, CKE1_A, CKE0_B, CKE1_B	Input	**Clock enable:** CKE HIGH activates and CKE LOW deactivates the internal clock signals, input buffers, and output drivers. Power-saving modes are entered and exited via CKE transitions. CKE is sampled at the rising edge of CK.
CS0_A, CS1_A, CS0_B, CS1_B	Input	**Chip select:** Each channel (A, B) has its own CS signals.
CA[5:0]_A, CA[5:0]_B	Input	**Command/Address inputs:** Provide the command and address inputs according to the command truth table. Each channel (A, B) has its own CA signals.
ODT_CA_A, ODT_CA_B	Input	**CA ODT control:** The ODT_CA pin is used in conjunction with the mode register to turn on/off the on-die termination for CA pins. It is bonded to V_{DD2} within the package, or at the package ball, for the terminating rank, and the non-terminating ranks are bonded to V_{SS} (or left floating with a weak pull-down on the DRAM die). The terminating rank is the DRAM that terminates the CA bus for all die on the same channel.
DQ[15:0]_A, DQ[15:0]_B	I/O	**Data input/output:** Bidirectional data bus.
DQS[1:0]_t_A, DQS[1:0]_c_A, DQS[1:0]_t_B, DQS[1:0]_c_B	I/O	**Data strobe:** DQS_t and DQS_c are bi-directional differential output clock signals used to strobe data during a READ or WRITE. The data strobe is generated by the DRAM for a READ and is edge-aligned with data. The data strobe is generated by the SoC memory controller for a WRITE and is trained to precede data. Each byte of data has a data strobe signal pair. Each channel (A, B) has its own DQS_t and DQS_c strobes.
DMI[1:0]_A, DMI[1:0]_B	I/O	**Data mask/Data bus inversion:** DMI is a dual use bi-directional signal used to indicate data to be masked, and data which is inverted on the bus. For data bus inversion (DBI), the DMI signal is driven HIGH when the data on the data bus is inverted, or driven LOW when the data is in its normal state. DBI can be disabled via a mode register setting. For data mask, the DMI signal is used in combination with the data lines to indicate data to be masked in a MASK WRITE command (see the Data Mask (DM) and Data Bus Inversion (DBI) sections for details). The data mask function can be disabled via a mode register setting. Each byte of data has a DMI signal. Each channel has its own DMI signals.
ZQ0, ZQ1	Reference	**ZQ calibration reference:** Used to calibrate the output drive strength and the termination resistance. The ZQ pin shall be connected to V_{DDQ} through a 240 ohms ±1% resistor.
V_{DDQ}, V_{DD1}, V_{DD2}	Supply	**Power supplies:** Isolated on the die for improved noise immunity.
V_{SS}	Supply	**Ground reference:** Power supply ground reference.
RESET_n	Input	**RESET:** When asserted LOW, the RESET pin resets all channels of the die.
DNU	–	**Do not use:** Must be grounded or left floating.
NC	–	**No connect:** Not internally connected.

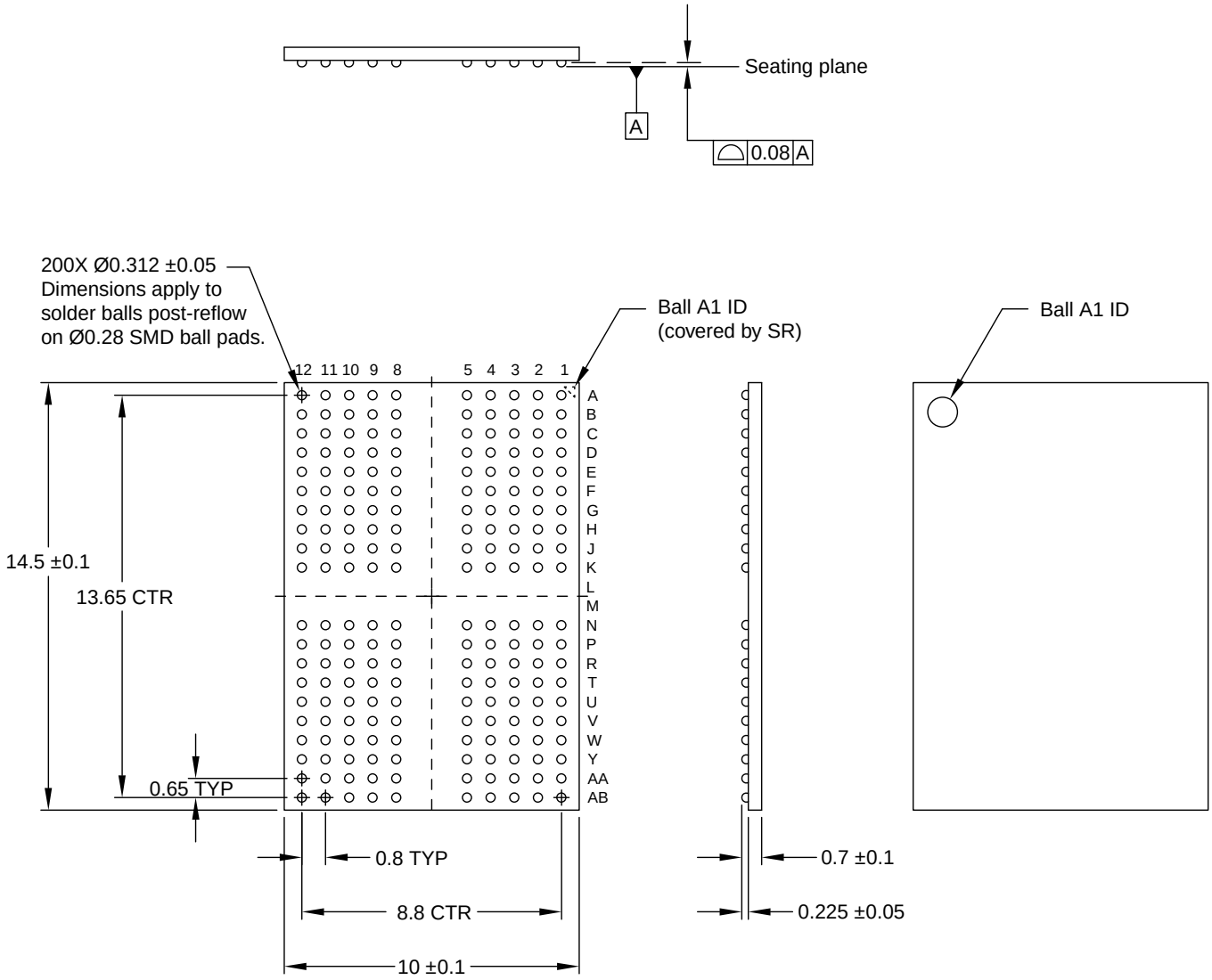
Package Dimensions

Figure 4: 200-Ball VFBGA – 10mm x 14.5mm (Package Code: DT)



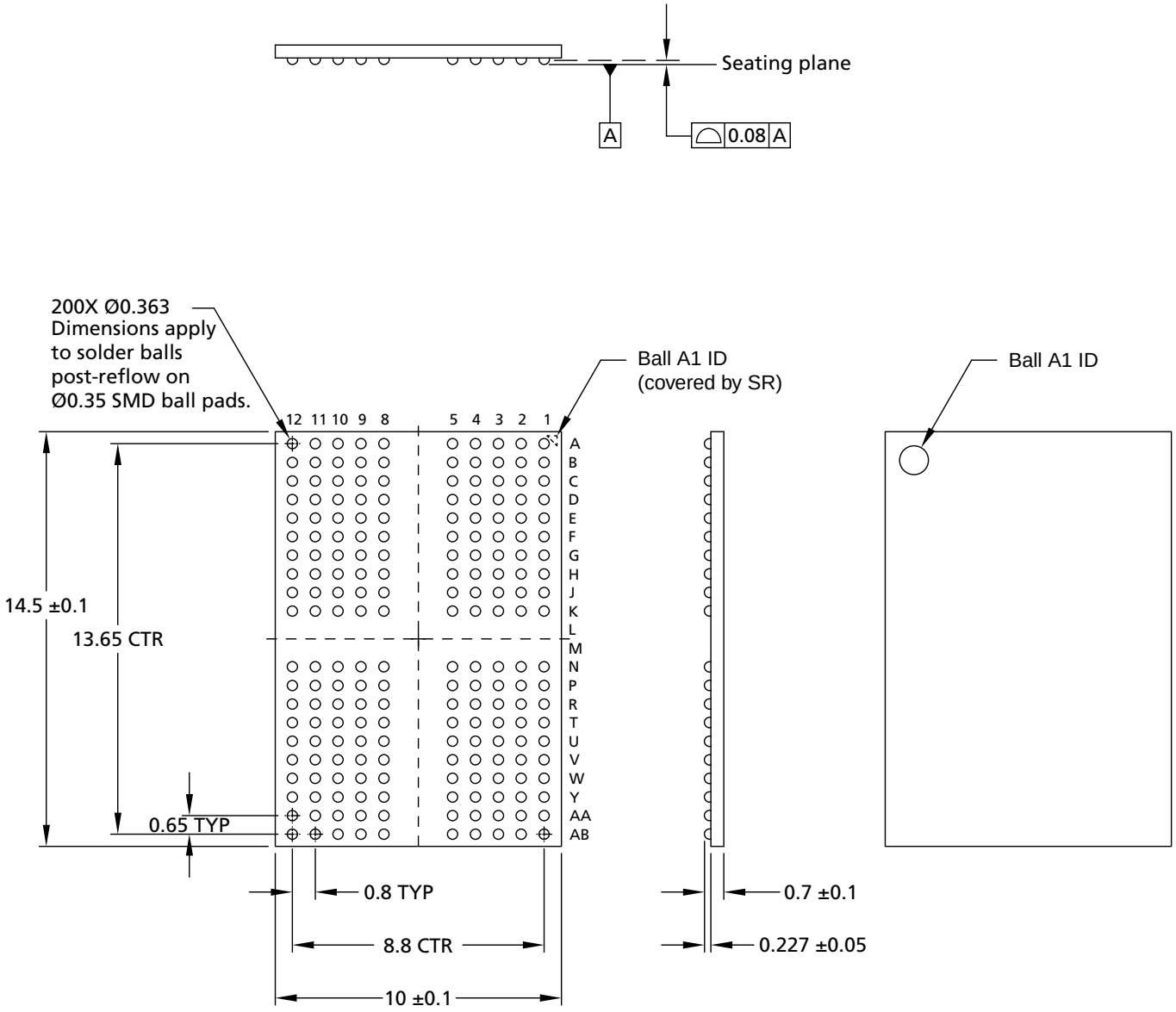
Notes: 1. All dimensions are in millimeters.
2. Solder ball composition: SAC302 with NiAu pads (96.8% Sn, 3Ag, 0.2% Cu).

Figure 5: 200-Ball WFBGA – 10mm x 14.5mm (Package Code: NP)



Notes: 1. All dimensions are in millimeters.
2. Solder ball composition: SAC302 with NiAu pads (96.8% Sn, 3Ag, 0.2% Cu).

Figure 6: 200-Ball WFBGA – 10mm x 14.5mm (Package Code: DS)



Notes: 1. All dimensions are in millimeters.
2. Solder ball composition: SAC302 with NiAu pads (96.8% Sn, 3Ag, 0.2% Cu).

MR0, MR[6:3], MR8, MR13 Readout

Table 5: Mode Register Contents

Mode Register	OP7	OP6	OP5	OP4	OP3	OP2	OP1	OP0
MR0								**REF**
	0b: Both legacy and modified refresh mode supported							
MR3						**PPRP**		
	0b: PPR protection disabled (default) 1b: Reserved							
MR4					**SR Abort**			
	0b: Disable (default) 1b: Reserved							
MR5	**Manufacturer ID**							
	1111 1111b : Micron							
MR6	**Revision ID1**							
	0000 0000b: Revision A							
MR8			**Density**					
	OP[5:2] = 0000b: 4Gb per die (2Gb per channel)							
MR13						**VRO**		
	0b: Normal operation (default) 1b: Output the $V_{REF(CA)}$ value on DQ7 and $V_{REF(DQ)}$ value on DQ6							

Notes: 1. The contents of MR0, MR[6:3], MR8, and MR13 will reflect information specific to each in these packages.
2. Other bits not defined above and other mode registers are referred to in Mode Register Assignments and Definitions section.

I_{DD} Parameters

Refer to I_{DD} Specification Parameters and Test Conditions section for detailed conditions.

Table 6: I_{DD} Specifications – Single-Die (T_C = –30°C to +85°C)

V_{DD2}, V_{DDQ} = 1.06–1.17V; V_{DD1} = 1.70–1.95V

Parameter	Supply	T_C	Unit	Notes
		3733 Mbps		
I_{DD01}	V_{DD1}	5	mA	
I_{DD02}	V_{DD2}	60		
I_{DD0Q}	V_{DDQ}	0.8		
I_{DD2P1}	V_{DD1}	2	mA	
I_{DD2P2}	V_{DD2}	2		
I_{DD2PQ}	V_{DDQ}	0.8		
I_{DD2PS1}	V_{DD1}	2	mA	
I_{DD2PS2}	V_{DD2}	2		
I_{DD2PSQ}	V_{DDQ}	0.8		
I_{DD2N1}	V_{DD1}	2	mA	
I_{DD2N2}	V_{DD2}	28		
I_{DD2NQ}	V_{DDQ}	0.8		
I_{DD2NS1}	V_{DD1}	2	mA	
I_{DD2NS2}	V_{DD2}	23		
I_{DD2NSQ}	V_{DDQ}	0.8		
I_{DD3P1}	V_{DD1}	2	mA	
I_{DD3P2}	V_{DD2}	7		
I_{DD3PQ}	V_{DDQ}	0.8		
I_{DD3PS1}	V_{DD1}	2	mA	
I_{DD3PS2}	V_{DD2}	7		
I_{DD3PSQ}	V_{DDQ}	0.8		
I_{DD3N1}	V_{DD1}	2	mA	
I_{DD3N2}	V_{DD2}	37		
I_{DD3NQ}	V_{DDQ}	0.8		
I_{DD3NS1}	V_{DD1}	2	mA	
I_{DD3NS2}	V_{DD2}	31		
I_{DD3NSQ}	V_{DDQ}	0.8		
I_{DD4R1}	V_{DD1}	3	mA	
I_{DD4R2}	V_{DD2}	470		
I_{DD4RQ}	V_{DDQ}	289		
I_{DD4W1}	V_{DD1}	3	mA	
I_{DD4W2}	V_{DD2}	388		
I_{DD4WQ}	V_{DDQ}	122		

Table 6: I_{DD} Specifications – Single-Die (T_C = –30°C to +85°C) (Continued)

Parameter	Supply	T_C	Unit	Notes
		3733 Mbps		
I_{DD51}	V_{DD1}	12	mA	
I_{DD52}	V_{DD2}	102		
I_{DD5Q}	V_{DDQ}	0.8		
I_{DD5AB1}	V_{DD1}	2	mA	
I_{DD5AB2}	V_{DD2}	32		
I_{DD5ABQ}	V_{DDQ5}	0.8		
I_{DD5PB1}	V_{DD1}	2	mA	
I_{DD5PB2}	V_{DD2}	32		
I_{DD5PBQ}	V_{DDQ}	0.8		

Notes: 1. I_{DD} values reflect dual-channel operation with the same pattern for each channel.
2. Published I_{DD} values except I_{DD4RQ} are the maximum of the distribution of the arithmetic mean. Refer to another note for I_{DD4RQ}. And refer to another table for I_{DD6}.
3. I_{DD4RQ} value is reference only. Typical value. DBI disabled; $V_{OH} = V_{DDQ}/3$, T_C = 25°C.
4. IDD values apply to components marked with date codes later than or equal to '4O'.

Table 7: I_{DD} Specifications – Single-Die (T_C = –40°C to +95°C)

V_{DD2}, V_{DDQ} = 1.06–1.17V; V_{DD1} = 1.70–1.95V

Parameter	Supply	T_C	Unit	Notes
		3733 Mbps		
I_{DD01}	V_{DD1}	5	mA	
I_{DD02}	V_{DD2}	62		
I_{DD0Q}	V_{DDQ}	0.8		
I_{DD2P1}	V_{DD1}	2	mA	
I_{DD2P2}	V_{DD2}	2		
I_{DD2PQ}	V_{DDQ}	0.8		
I_{DD2PS1}	V_{DD1}	2	mA	
I_{DD2PS2}	V_{DD2}	2		
I_{DD2PSQ}	V_{DDQ}	0.8		
I_{DD2N1}	V_{DD1}	2	mA	
I_{DD2N2}	V_{DD2}	29		
I_{DD2NQ}	V_{DDQ}	0.8		
I_{DD2NS1}	V_{DD1}	2	mA	
I_{DD2NS2}	V_{DD2}	24		
I_{DD2NSQ}	V_{DDQ}	0.8		
I_{DD3P1}	V_{DD1}	2	mA	
I_{DD3P2}	V_{DD2}	8		
I_{DD3PQ}	V_{DDQ}	0.8		
I_{DD3PS1}	V_{DD1}	2	mA	
I_{DD3PS2}	V_{DD2}	8		
I_{DD3PSQ}	V_{DDQ}	0.8		

Table 7: I_{DD} Specifications – Single-Die (T_C = –40°C to +95°C) (Continued)

Parameter	Supply	T_C	Unit	Notes
		3733 Mbps		
I_{DD3N1}	V_{DD1}	2	mA	
I_{DD3N2}	V_{DD2}	39		
I_{DD3NQ}	V_{DDQ}	0.8		
I_{DD3NS1}	V_{DD1}	2	mA	
I_{DD3NS2}	V_{DD2}	33		
I_{DD3NSQ}	V_{DDQ}	0.8		
I_{DD4R1}	V_{DD1}	3	mA	
I_{DD4R2}	V_{DD2}	471		
I_{DD4RQ}	V_{DDQ}	289		
I_{DD4W1}	V_{DD1}	3	mA	
I_{DD4W2}	V_{DD2}	391		
I_{DD4WQ}	V_{DDQ}	122		
I_{DD51}	V_{DD1}	12	mA	
I_{DD52}	V_{DD2}	104		
I_{DD5Q}	V_{DDQ}	0.8		
I_{DD5AB1}	V_{DD1}	2	mA	
I_{DD5AB2}	V_{DD2}	33		
I_{DD5ABQ}	V_{DDQ5}	0.8		
I_{DD5PB1}	V_{DD1}	2	mA	
I_{DD5PB2}	V_{DD2}	33		
I_{DD5PBQ}	V_{DDQ}	0.8		

Notes: 1. I_{DD} values reflect dual-channel operation with the same pattern for each channel.
2. Published I_{DD} values except I_{DD4RQ} are the maximum of the distribution of the arithmetic mean. Refer to another note for I_{DD4RQ}. And refer to another table for I_{DD6}.
3. I_{DD4RQ} value is reference only. Typical value. DBI disabled; $V_{OH} = V_{DDQ}/3$, T_C = 25°C.
4. IDD values apply to components marked with date codes later than or equal to '4O'.

Table 8: I_{DD6} Full-Array Self Refresh Current

Temperature	Supply	Self Refresh Current				Unit	Notes
		Full-Array	1/2-Array	1/4-Array	1/8-Array		
25°C	V_{DD1}	0.12	0.10	0.10	0.09	mA	
	V_{DD2}	0.30	0.21	0.17	0.15		
	V_{DDQ}	0.01	0.01	0.01	0.01		
45°C	V_{DD1}	0.18	0.14	0.13	0.12	mA	
	V_{DD2}	0.80	0.55	0.43	0.37		
	V_{DDQ}	0.01	0.01	0.01	0.01		
65°C	V_{DD1}	0.23	0.18	0.16	0.15	mA	
	V_{DD2}	1.31	0.89	0.68	0.58		
	V_{DDQ}	0.01	0.01	0.01	0.01		
85°C	V_{DD1}	2.00	2.00	2.00	2.00	mA	
	V_{DD2}	4.00	3.00	3.00	2.00		
	V_{DDQ}	0.80	0.80	0.80	0.80		
95°C	V_{DD1}	2.00	2.00	2.00	2.00	mA	
	V_{DD2}	5.00	4.00	3.00	3.00		
	V_{DDQ}	0.80	0.80	0.80	0.80		

Notes: 1. V_{DD2}, V_{DDQ} = 1.06–1.17V; V_{DD1} = 1.70–1.95V
2. I_{DD} values reflect dual-channel operation with the same pattern for each channel.
3. I_{DD6} 25°C, I_{DD6} 45°C, I_{DD6} 65°C and partial array (half-array, quarter-array and eighth-array) at all temperatures are the typical values in the distribution with nominal V_{DD} and reference-only values. I_{DD6} full-array at 95°C are the maximum guaranteed I_{DD} values considering the worst-case conditions of process, temperature, and voltage.
4. IDD values apply to components marked with date codes later than or equal to '4O'.

Functional Description

The Mobile Low-Power DDR4 SDRAM (LPDDR4) is a high-speed CMOS, dynamic random-access memory internally configured with either 1 or 2 channels. Each channel is comprised of 16 DQs and 8 banks.

LPDDR4 uses a 2-tick, single-data-rate (SDR) protocol on the CA bus to reduce the number of input signals in the system. The term "2-tick" means that the command/address is decoded across two transactions, such that half of the command/address is captured with each of two consecutive rising edges of CK. The 6-bit CA bus contains command, address, and bank information. Some commands such as READ, WRITE, MASKED WRITE, and ACTIVATE require two consecutive 2-tick SDR commands to complete the instruction.

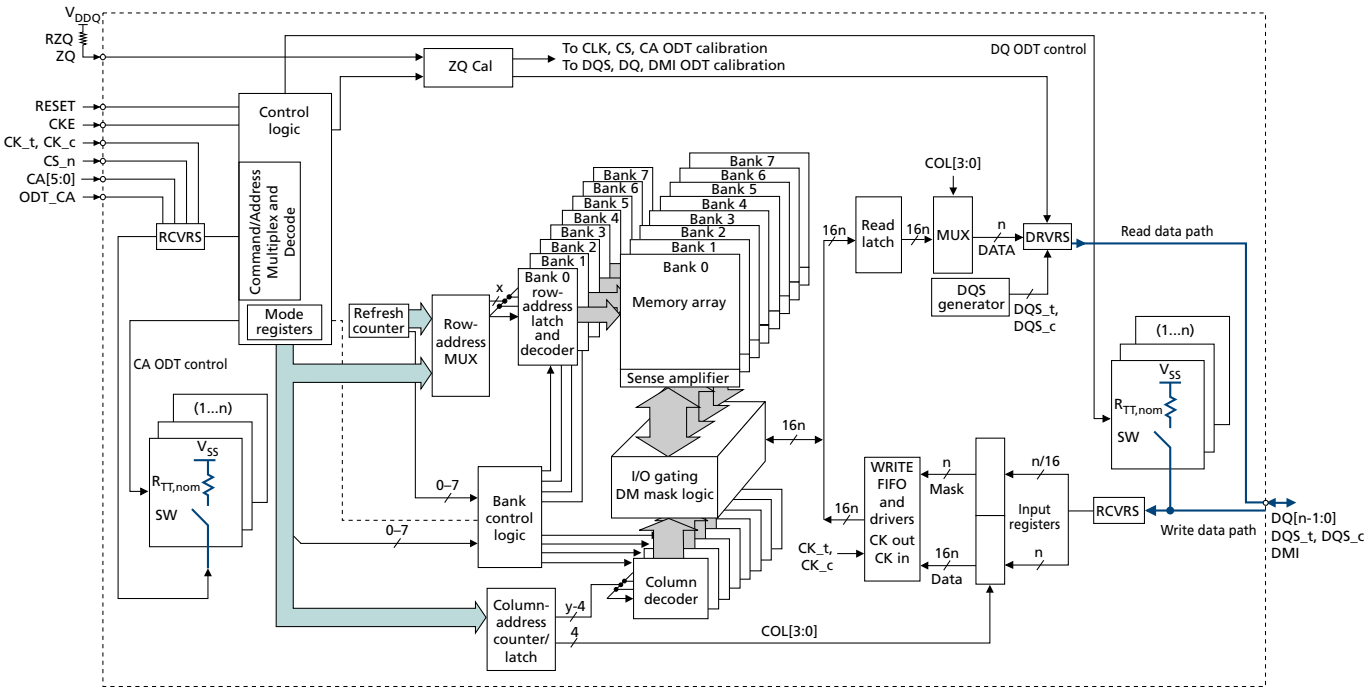
LPDDR4 uses a double-data-rate (DDR) protocol on the DQ bus to achieve high-speed operation. The DDR interface transfers two data bits to each DQ lane in one clock cycle and is matched to a 16*n*-prefetch DRAM architecture. A write/read access consists of a single 16*n*-bit-wide data transfer to/from the DRAM core and 16 corresponding *n*-bit-wide data transfers at the I/O pins.

Read and write accesses to the device are burst-oriented. Accesses start at a selected column address and continue for a programmed number of columns in a programmed sequence.

Accesses begin with the registration of an ACTIVATE command to open a row in the memory core, followed by a WRITE or READ command to access column data within the open row. The address and bank address (BA) bits registered by the ACTIVATE command are used to select the bank and row to be opened. The address and BA bits registered with the WRITE or READ command are used to select the bank and the starting column address for the burst access.

Prior to normal operation, the LPDDR4 SDRAM must be initialized. Following sections provide detailed information about device initialization, register definition, command descriptions and device operations.

Figure 7: Functional Block Diagram



Monolithic Device Addressing

The table below includes all monolithic device addressing options defined by JEDEC. Under the SDRAM Addressing heading near the beginning of this data sheet are addressing details for this product data sheet.

Table 9: Monolithic Device Addressing – Dual-Channel Die

Memory Density (Per Die)		4Gb	6Gb	8Gb	12Gb	16Gb	24Gb	32Gb
Memory density (per channel)		2Gb	3Gb	4Gb	6Gb	8Gb	12Gb	16Gb
Configuration		16Mb × 16DQ × 8 banks × 2 channels	24Mb × 16DQ × 8 banks × 2 channels	32Mb × 16DQ × 8 banks × 2 channels	48Mb × 16DQ × 8 banks × 2 channels	64Mb × 16DQ × 8 banks × 2 channels	96Mb × 16DQ × 8 banks × 2 channels	128Mb × 16DQ × 8 banks × 2 channels
Number of channels (per die)		2	2	2	2	2	2	2
Number of banks (per channel)		8	8	8	8	8	8	8
Array prefetch (bits, per channel)		256	256	256	256	256	256	256
Number of rows (per channel)		16,384	24,576	32,768	49,152	65,536	98,304	131,072
Number of columns (fetch boundaries)		64	64	64	64	64	64	64
Page size (bytes)		2048	2048	2048	2048	2048	2048	2048
Channel density (bits per channel)		2,147,483,648	3,221,225,472	4,294,967,296	6,442,450,944	8,589,934,592	12,884,901,888	17,179,869,184
Total density (bits per die)		4,294,967,296	6,442,450,944	8,589,934,592	12,884,901,888	17,179,869,184	25,769,803,776	34,359,738,368
Bank address		BA[2:0]	BA[2:0]	BA[2:0]	BA[2:0]	BA[2:0]	BA[2:0]	BA[2:0]
×16	Row add	R[13:0]	R[14:0] (R13 = 0 when R14 = 1)	R[14:0]	R[15:0] (R14 = 0 when R15 = 1)	R[15:0]	R[16:0] (R15 = 0 when R16 = 1)	R[16:0]
	Col. add	C[9:0]	C[9:0]	C[9:0]	C[9:0]	C[9:0]	C[9:0]	C[9:0]
Burst starting address boundary		64-bit	64-bit	64-bit	64-bit	64-bit	64-bit	64-bit

Table 10: Monolithic Device Addressing – Single-Channel Die

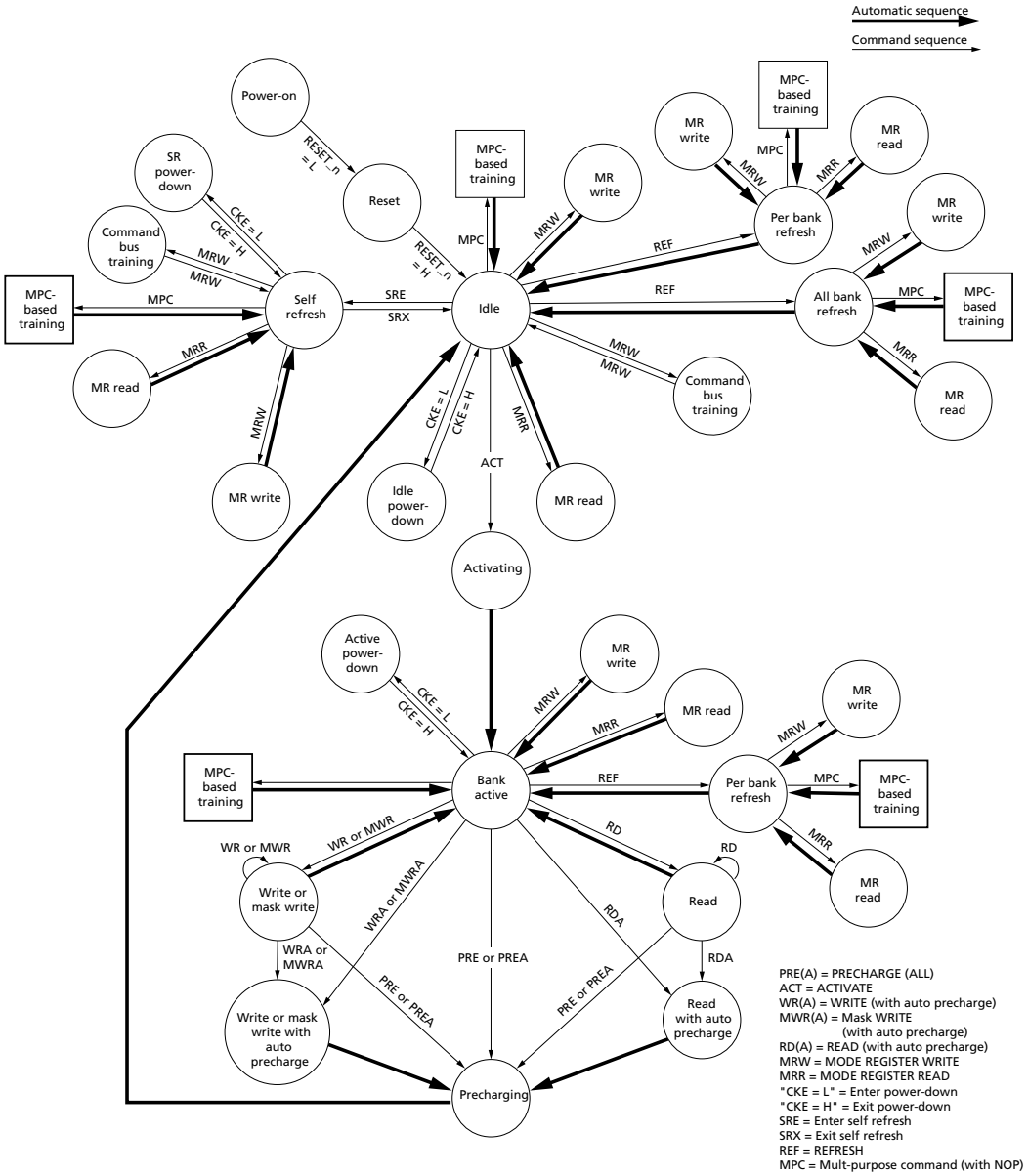
Memory Density (Per Die)		2Gb	3Gb	4Gb	6Gb	8Gb	12Gb	16Gb
Memory density (per channel)		2Gb	3Gb	4Gb	6Gb	8Gb	12Gb	16Gb
Configuration		16Mb × 16 DQ × 8 banks	24Mb × 16 DQ × 8 banks	32Mb × 16 DQ × 8 banks	48Mb × 16 DQ × 8 banks	64Mb × 16 DQ × 8 banks	96Mb × 16 DQ × 8 banks	128Mb × 16 DQ × 8 banks
Number of channels (per die)		1	1	1	1	1	1	1
Number of banks (per channel)		8	8	8	8	8	8	8
Array prefetch (bits, per channel)		256	256	256	256	256	256	256
Number of rows (per channel)		16,384	24,576	32,768	49,152	65,536	98,304	131,072
Number of columns (fetch boundaries)		64	64	64	64	64	64	64
Page size (bytes)		2048	2048	2048	2048	2048	2048	2048
Channel density (bits per channel)		2,147,483,648	3,221,225,472	4,294,967,296	6,442,450,944	8,589,934,592	12,884,901,888	17,179,869,184
Total density (bits per die)		2,147,483,648	3,221,225,472	4,294,967,296	6,442,450,944	8,589,934,592	12,884,901,888	17,179,869,184
Bank address		BA[2:0]	BA[2:0]	BA[2:0]	BA[2:0]	BA[2:0]	BA[2:0]	BA[2:0]
×16	Row add	R[13:0]	R[14:0] (R13 = 0 when R14 = 1)	R[14:0]	R[15:0] (R14 = 0 when R15 = 1)	R[15:0]	R[16:0] (R15 = 0 when R16 = 1)	R[16:0]
	Col. add	C[9:0]	C[9:0]	C[9:0]	C[9:0]	C[9:0]	C[9:0]	C[9:0]
Burst starting address boundary		64-bit	64-bit	64-bit	64-bit	64-bit	64-bit	64-bit

Notes: 1. The lower two column addresses (C[1:0]) are assumed to be zero and are not transmitted on the CA bus.
2. Row and column address values on the CA bus that are not used for a particular density should be at valid logic levels.
3. For non-binary memory densities, only a quarter of the row address space is invalid. When the MSB address bit is HIGH, then the MSB - 1 address bit must be LOW.

Simplified Bus Interface State Diagram

The state diagram provides a simplified illustration of the bus interface, supported state transitions, and the commands that control them. For a complete description of device behavior, use the information provided in the state diagram with the truth tables and timing specifications. The truth tables describe device behavior and applicable restrictions when considering the actual state of all banks. For command descriptions, see the Commands and Timing section.

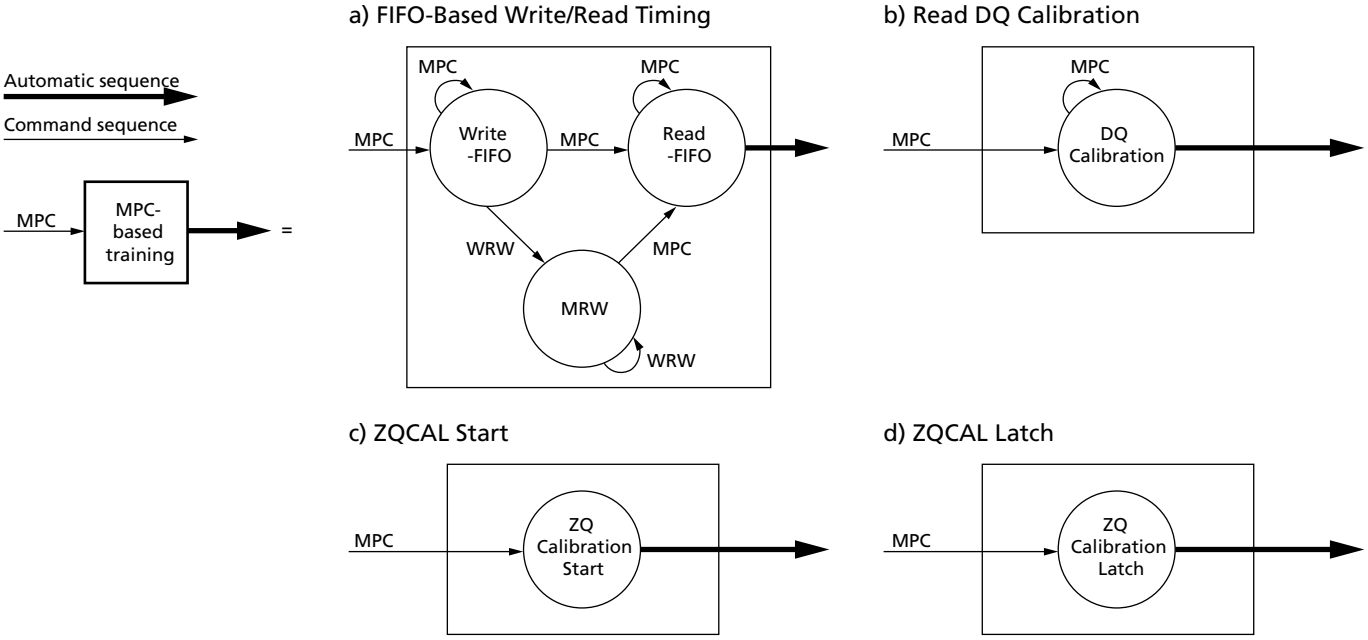
Figure 8: Simplified State Diagram



Notes: 1. From the self refresh state, the device can enter power-down, MRR, MRW, or any of the training modes initiated with the MPC command. See the Self Refresh section.
2. All banks are precharged in the idle state.
3. In the case of using an MRW command to enter a training mode, the state machine will not automatically return to the idle state at the conclusion of training. See the applicable training section for more information.

4. In the case of an MPC command to enter a training mode, the state machine may not automatically return to the idle state at the conclusion of training. See the applicable training section for more information.
5. This diagram is intended to provide an overview of the possible state transitions and commands to control them; however, it does not contain the details necessary to operate the device. In particular, situations involving more than one bank are not captured in complete detail.
6. States that have an "automatic return" and can be accessed from more than one prior state (that is, MRW from either idle or active states) will return to the state where they were initiated (that is, MRW from idle will return to idle).
7. The RESET pin can be asserted from any state and will cause the device to enter the reset state. The diagram shows RESET applied from the power-on and idle states as an example, but this should not be construed as a restriction on RESET.
8. MRW commands from the active state cannot change operating parameters of the device that affect timing. Mode register fields which may be changed via MRW from the active state include: MR1-OP[3:0], MR1-OP[7], MR3-OP[7:6], MR10-OP[7:0], MR11-OP[7:0], MR13-OP[5], MR15-OP[7:0], MR16-OP[7:0], MR17-OP[7:0], MR20-OP[7:0], and MR22-OP[4:0].

Figure 9: Simplified State Diagram



Power-Up and Initialization

To ensure proper functionality for power-up and reset initialization, default values for the MR settings are provided in the table below.

Table 11: Mode Register Default Settings

Item	Mode Register Setting	Default Setting	Description
FSP-OP/WR	MR13 OP[7:6]	00b	FSP-OP/WR[0] are enabled
WLS	MR2 OP[6]	0b	WRITE latency set A is selected
WL	MR2 OP[5:3]	000b	WL = 4
RL	MR2 OP[2:0]	000b	RL = 6, *n*RTP = 8
*n*WR	MR1 OP[6:4]	000b	*n*WR = 6
DBI-WR/RD	MR3 OP[7:6]	00b	Write and read DBI are disabled

Table 11: Mode Register Default Settings (Continued)

Item	Mode Register Setting	Default Setting	Description
CA ODT	MR11 OP[6:4]	000b	CA ODT is disabled
DQ ODT	MR11 OP[2:0]	000b	DQ ODT is disabled
$V_{REF(CA)}$ setting	MR12 OP[6]	1b	$V_{REF(CA)}$ range[1] is enabled
$V_{REF(CA)}$ value	MR12 OP[5:0]	001101b	Range1: 27.2% of V_{DD2}
$V_{REF(DQ)}$ setting	MR14 OP[6]	1b	$V_{REF(DQ)}$ range[1] enabled
$V_{REF(DQ)}$ value	MR14 OP[5:0]	001101b	Range1: 27.2% of V_{DDQ}

The following sequence must be used to power up the device. Unless specified otherwise, this procedure is mandatory. The power-up sequence of all channels must proceed simultaneously.

Voltage Ramp

1. While applying power (after Ta), RESET_n should be held LOW (≤0.2 × V_{DD2}), and all other inputs must be between $V_{IL,min}$ and $V_{IH,max}$. The device outputs remain at High-Z while RESET_n is held LOW. Power supply voltage ramp requirements are provided in the table below. V_{DD1} must ramp at the same time or earlier than V_{DD2}. V_{DD2} must ramp at the same time or earlier than V_{DDQ}.

Table 12: Voltage Ramp Conditions

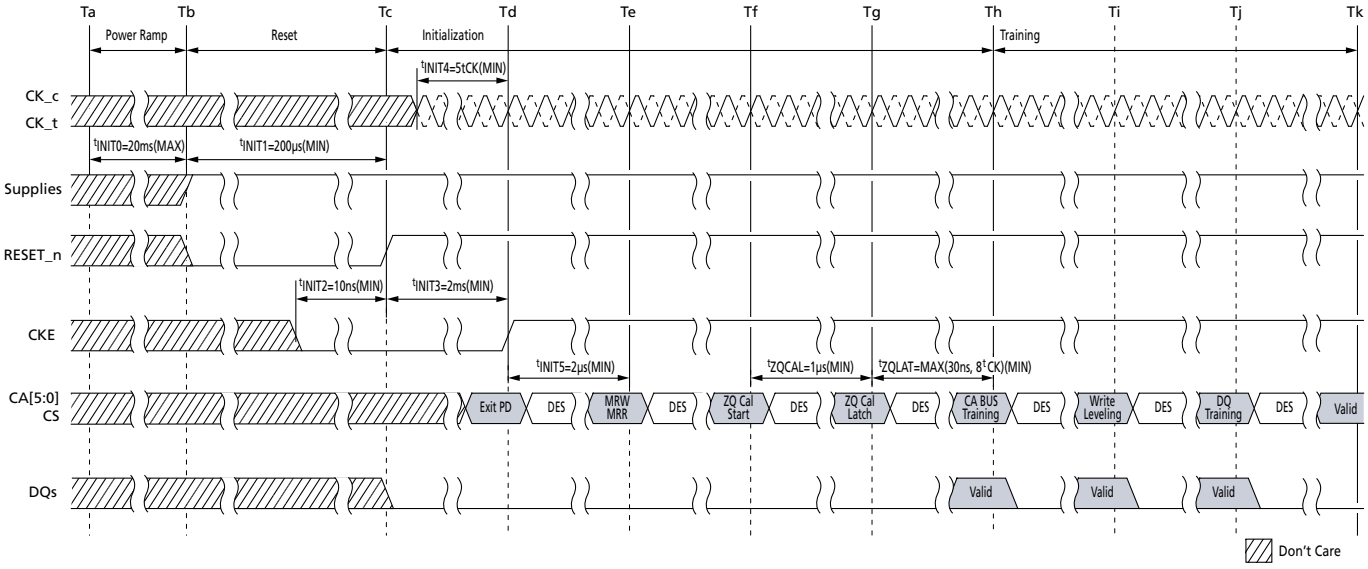
After...	Applicable Conditions
Ta is reached	V_{DD1} must be greater than V_{DD2}
	V_{DD2} must be greater than V_{DDQ} - 200mV

Notes: 1. Ta is the point when any power supply first reaches 300mV.
2. Voltage ramp conditions in above table apply between Ta and power-off (controlled or uncontrolled).
3. Tb is the point at which all supply and reference voltages are within their defined operating ranges.
4. Power ramp duration ^{t}INIT0 (Tb–Ta) must not exceed 20ms.
5. The voltage difference between any V_{SS} and V_{SSQ} must not exceed 100mV.

2. Following completion of the of the voltage ramp (Tb), RESET_n must be held LOW for ^{t}INIT1. DQ, DMI, DQS_t, and DQS_c voltage levels must be between V_{SSQ} and V_{DDQ} during voltage ramp to avoid latch-up. CK_t and CK_c, CS, and CA input levels must be between V_{SS} and V_{DD2} during voltage ramp to avoid latch-up. Voltage ramp power supply requirements are provided in the table below.

3. Beginning at Tb, RESET_n must remain LOW for at least ^{t}INIT1(Tc), after which RESET_n can be de-asserted to HIGH(Tc). At least 10ns before CKE de-assertion, CKE is required to be set LOW. All other input signals are Don't Care.

Figure 10: Voltage Ramp and Initialization Sequence



Note: 1. Training is optional and may be done at the system designer's discretion. The order of training may be different than what is shown here.

4. After RESET_n is de-asserted(Tc), wait at least ^{t}INIT3 before activating CKE. CK_t, CK_c must be started and stabilized for ^{t}INIT4 before CKE goes active(Td). CS must remain LOW when the controller activates CKE.

5. After CKE is set to HIGH, wait a minimum of ^{t}INIT5 to issue any MRR or MRW commands(Te). For MRR and MRW commands, the clock frequency must be within the range defined for ^{t}CKb. Some AC parameters (for example, ^{t}DQSCK) could have relaxed timings (such as ^{t}DQSCKb) before the system is appropriately configured.

6. After completing all MRW commands to set the pull-up, pull-down, and Rx termination values, the controller can issue the ZQCAL START command to the memory(Tf). This command is used to calibrate the V_{OH} level and the output impedance over process, voltage, and temperature. In systems where more than one device share one external ZQ resistor, the controller must not overlap the ZQ calibration sequence of each device. The ZQ calibration sequence is completed after ^{t}ZQCAL (Tg). The ZQCAL LATCH command must be issued to update the DQ drivers and DQ + CA ODT to the calibrated values.

7. After ^{t}ZQLAT is satisfied (Th), the command bus (internal $V_{REF(CA)}$, CS, and CA) should be trained for high-speed operation by issuing an MRW command (command bus training mode). This command is used to calibrate the device's internal V_{REF} and align CS/CA with CK for high-speed operation. The device will power-up with receivers configured for low-speed operations and with $V_{REF(CA)}$ set to a default factory setting. Normal device operation at clock speeds higher than ^{t}CKb may not be possible until command bus training is complete. The command bus training MRW command uses the CA bus as inputs for the calibration data stream, and it outputs the results asynchronously on the DQ bus. See command bus training in the MRW section for information on how to enter/exit the training mode.

8. After command bus training, the controller must perform write leveling. Write leveling mode is enabled when MR2 OP[7] is HIGH(Ti). See the Write Leveling section for a detailed description of the write leveling entry and exit sequence. In write leveling mode, the controller adjusts write DQS timing to the point where the device recognizes the start of write DQ data burst with desired WRITE latency.

9. After write leveling, the DQ bus (internal $V_{REF(DQ)}$, DQS, and DQ) should be trained for high-speed operation using the MPC TRAINING commands and by issuing MRW commands to adjust $V_{REF(DQ)}$.

The device will power-up with receivers configured for low-speed operations and with $V_{REF(DQ)}$ set to a default factory setting. Normal device operation at clock speeds higher than ^{t}CKb should not be attempted until DQ bus training is complete. The MPC[READ DQ CALIBRATION] command is used together with MPC[READ-FIFO] or MPC[WRITE-FIFO] commands to train the DQ bus without disturbing the memory array contents. See the DQ Bus Training section for more information on the DQ bus training sequence.

10. At Tk, the device is ready for normal operation and is ready to accept any valid command. Any mode registers that have not previously been configured for normal operation should be written at this time.

Table 13: Initialization Timing Parameters

Parameter	Min	Max	Unit	Comment
^{t}INIT0	–	20	ms	Maximum voltage ramp time
^{t}INIT1	200	–	µs	Minimum RESET_n LOW time after completion of voltage ramp
^{t}INIT2	10	–	ns	Minimum CKE LOW time before RESET_n goes HIGH
^{t}INIT3	2	–	ms	Minimum CKE LOW time after RESET_n goes HIGH
^{t}INIT4	5	–	^{t}CK	Minimum stable clock before first CKE HIGH
^{t}INIT5	2	–	µs	Minimum idle time before first MRW/MRR command
^{t}CKb	Note[1, 2]	Note[1, 2]	ns	Clock cycle time during boot

Notes: 1. Minimum ^{t}CKb guaranteed by DRAM test is 18ns.
2. The system may boot at a higher frequency than dictated by minimum ^{t}CKb. The higher boot frequency is system dependent.

Reset Initialization With Stable Power

The following sequence is required for RESET at no power interruption initialization.

1. Assert RESET_n below $0.2 \times V_{DD2}$ anytime when reset is needed. RESET_n needs to be maintained for minimum ^{t}PW_RESET. CKE must be pulled LOW at least 10ns before de-asserting RESET_n.
2. Repeat steps 4–10 in Voltage Ramp section.

Table 14: Reset Timing Parameter

Parameter	Value		Unit	Comment
	Min	Max		
^{t}PW_RESET	100	–	ns	Minimum RESET_n LOW time for reset initialization with stable power

Power-Off Sequence

Controlled Power-Off

While powering off, CKE must be held LOW ($\leq 0.2 \times V_{DD2}$); all other inputs must be between $V_{IL,min}$ and $V_{IH,max}$. The device outputs remain at High-Z while CKE is held LOW.

DQ, DMI, DQS_t, and DQS_c voltage levels must be between V_{SSQ} and V_{DDQ} during the power-off sequence to avoid latch-up. CK_t, CK_c, CS, and CA input levels must be between V_{SS} and V_{DD2} during the power-off sequence to avoid latch-up.

Tx is the point where any power supply drops below the minimum value specified in the minimum DC Operating Condition.

Tz is the point where all power supplies are below 300mV. After Tz, the device is powered off.

Table 15: Power Supply Conditions

The voltage difference between V_{SS} and V_{SSQ} must not exceed 100mV

Between...	Applicable Conditions
Tx and Tz	V_{DD1} must be greater than V_{DD2}
	V_{DD2} must be greater than V_{DDQ} - 200mV

Uncontrolled Power-Off

When an uncontrolled power-off occurs, the following conditions must be met:

- At Tx, when the power supply drops below the minimum values specified in the Recommended DC Operating Conditions table, all power supplies must be turned off and all power supply current capacity must be at zero, except for any static charge remaining in the system.
- After Tz (the point at which all power supplies first reach 300mV), the device must power off. During this period, the relative voltage between power supplies is uncontrolled. V_{DD1} and V_{DD2} must decrease with a slope lower than 0.5 V/µs between Tx and Tz.

An uncontrolled power-off sequence can occur a maximum of 400 times over the life of the device.

Table 16: Power-Off Timing

Parameter	Symbol	Min	Max	Unit
Power-off ramp time	^{t}POFF	–	2	sec

Mode Registers

Mode Register Assignments and Definitions

Mode register definitions are provided in the Mode Register Assignments table. In the access column of the table, R indicates read-only; W indicates write-only; R/W indicates read- or write-capable or enabled. The MRR command is used to read from a register. The MRW command is used to write to a register.

Table 17: Mode Register Assignments

MR#	MA[5:0]	Function	Access	OP7	OP6	OP5	OP4	OP3	OP2	OP1	OP0	Link
0	00h	Device info	R	CATR	RFU	RFU	RZQI		RFU		REF	Go to MR0
1	01h	Device feature 1	W	RD-PST	*n*WR (for AP)			RD-PRE	WR-PRE	BL		Go to MR1
2	02h	Device feature 2	W	WR Lev	WLS	WL			RL			Go to MR2
3	03h	I/O config-1	W	DBI-WR	DBI-RD	PDDS			PPRP	WR-PST	PU-CAL	Go to MR3
4	04h	Refresh and training	R /W	TUF	Thermal offset		PPRE	SR abort	Refresh rate			Go to MR4
5	05h	Basic config-1	R	Manufacturer ID								Go to MR5
6	06h	Basic config-2	R	Revision ID1								Go to MR6
7	07h	Basic config-3	R	Revision ID2								Go to MR7
8	08h	Basic config-4	R	I/O width		Density				Type		Go to MR8
9	09h	Test mode	W	Vendor-specific test mode								Go to MR9
10	0Ah	I/O calibration	W	RFU							ZQ RST	Go to MR10

Table 17: Mode Register Assignments (Continued)

MR#	MA[5:0]	Function	Access	OP7	OP6	OP5	OP4	OP3	OP2	OP1	OP0	Link
11	0Bh	ODT	W	RFU	CA ODT			RFU	DQ ODT			Go to MR11
12	0Ch	$V_{REF(CA)}$	R/W	RFU	VR_{CA}	$V_{REF(CA)}$						Go to MR12
13	0Dh	Register control	W	FSP-OP	FSP-WR	DMD	RRO	VRCG	VRO	RPT	CBT	Go to MR13
14	0Eh	$V_{REF(DQ)}$	R/W	RFU	VR_{DQ}	$V_{REF(DQ)}$						Go to MR14
15	0Fh	DQI-LB	W	Lower-byte invert register for DQ calibration								Go to MR15
16	10h	PASR_Bank	W	PASR bank mask								Go to MR16
17	11h	PASR_Seg	W	PASR segment mask								Go to MR17
18	12h	IT-LSB	R	DQS oscillator count – LSB								Go to MR18
19	13h	IT-MSB	R	DQS oscillator count – MSB								Go to MR19
20	14h	DQI-UB	W	Upper-byte invert register for DQ calibration								Go to MR20
21	15h	Vendor use	W	RFU								Go to MR21
22	16h	ODT feature 2	W	RFU		ODTD-CA	ODTE-CS	ODTE-CK	SoC ODT			Go to MR22
23	17h	DQS oscillator stop	W	DQS oscillator run-time setting								Go to MR23
24	18h	TRR control	R/W	TRR mode	TRR mode BAn			Unltd MAC	MAC value			Go to MR24
25	19h	PPR resources	R	B7	B6	B5	B4	B3	B2	B1	B0	Go to MR25
26–31	1Ah~1Fh	–	–	Reserved for future use								
32	20h	DQ calibration pattern A	W	See DQ calibration section								Go to MR32
33–39	21h~27h	Do not use	–	Do not use								
40	28h	DQ calibration pattern B	W	See DQ calibration section								Go to MR40
41–47	29h~2Fh	Do not use	–	Do not use								
48–63	30h~3Fh	Reserved	–	Reserved for future use								

Notes: 1. RFU bits must be set to 0 during MRW commands.
2. RFU bits are read as 0 during MRR commands.
3. All mode registers that are specified as RFU or write-only shall return undefined data when read via an MRR command.

4. RFU mode registers must not be written.
5. Writes to read-only registers will not affect the functionality of the device.

Table 18: MR0 Device Feature 0 (MA[5:0] = 00h)

OP7	OP6	OP5	OP4	OP3	OP2	OP1	OP0
CATR	RFU		RZQI		RFU		REF

Table 19: MR0 Op-Code Bit Definitions

Register Information	Tag	Type	OP	Definition	Notes
Refresh mode	REF	Read only	OP[0]	0b: Both legacy and modified refresh mode supported 1b: Only modified refresh mode supported	
Built-in self-test for RZQ information	RZQI	Read only	OP[4:3]	00b: RZQ self-test not supported 01b: ZQ may connect to V_{SSQ} or float 10b: ZQ may short to V_{DDQ} 11b: ZQ pin self-test completed, no error condition detected (ZQ may not connect to V_{SSQ}, float, or short to V_{DDQ})	1–4
CA terminating rank	CATR	Read only	OP[7]	0b: CA for this rank is not terminated 1b: CA for this rank is terminated	

Notes: 1. RZQI, if supported, will be set upon completion of MPC[ZQCAL START] command. (^{t}ZQCAL after MPC[ZQCAL START] command.) RZQI value will be lost after reset.
2. If ZQ is connected to V_{SSQ} to set default calibration, OP[4:3] must be set to 01b. If ZQ is not connected to V_{SSQ}, either OP[4:3] = 01b or OP[4:3] = 10b might indicate a ZQ pin assembly error. It is recommended that the assembly error be corrected.
3. In the case of possible assembly error, the device will default to factory trim settings for R_{ON}, and will ignore ZQ CALIBRATION commands. In either case, the device may not function as intended.
4. If the ZQ pin self-test returns OP[4:3] = 11b, the device has detected a resistor connected to the ZQ pin. However, this result cannot be used to validate the ZQ resistor value or that the ZQ resistor meets the specified limits (that is, 240Ω±1%).

Table 20: MR1 Device Feature 1 (MA[5:0] = 01h)

OP7	OP6	OP5	OP4	OP3	OP2	OP1	OP0
RD-PST	*n*WR (for AP)			RD-PRE	WR-PRE	BL	

Table 21: MR1 Op-Code Bit Definitions

Feature	Type	OP	Definition	Notes
BL Burst length	Write only	OP[1:0]	00b: BL = 16 sequential (default) 01b: BL= 32 sequential 10b: BL = 16 or 32 sequential (on-the-fly) 11b: Reserved	1, 5, 6
WR-PRE Write preamble length	Write only	OP[2]	0b: Reserved 1b: WR preamble = 2 × ^{t}CK	5, 6
RD-PRE Read preamble type	Write only	OP[3]	0b: RD preamble = Static (default) 1b: RD preamble = Toggle	3, 5, 6

Table 21: MR1 Op-Code Bit Definitions (Continued)

Feature	Type	OP	Definition	Notes
*n*WR Write-recovery for auto-precharge command	Write only	OP[6:4]	000b: *n*WR = 6 (default) 001b: *n*WR = 10 010b: *n*WR = 16 011b: *n*WR = 20 100b: *n*WR = 24 101b: *n*WR = 30 110b: *n*WR = 34 111b: *n*WR = 40	2, 5, 6
RD-PST Read postamble length	Write only	OP[7]	0b: RD postamble = 0.5 × ^{t}CK (default) 1b: RD postamble = 1.5 × ^{t}CK	4, 5, 6

Notes: 1. Burst length on-the-fly can be set to either BL = 16 or BL = 32 by setting the BL bit in the command operands. See the Command Truth Table.
2. The programmed value of *n*WR is the number of clock cycles the device uses to determine the starting point of an internal precharge after a write burst with auto precharge (AP) enabled. See Frequency Ranges for RL, WL, and *n*WR Settings table.
3. For READ operations, this bit must be set to select between a toggling preamble and a non-toggling preamble. (See the Preamble section.)
4. OP[7] provides an optional READ postamble with an additional rising and falling edge of DQS_t. The optional postamble cycle is provided for the benefit of certain memory controllers.
5. There are two physical registers assigned to each bit of this MR parameter, designated set point 0 and set point 1. Only the registers for the set point determined by the state of the FSP-WR bit (MR13 OP[6]) will be written to with an MRW command to this MR address.
6. There are two physical registers assigned to each bit of this MR parameter, designated set point 0 and set point 1. The device will operate only according to the values stored in the registers for the active set point, that is, the set point determined by the state of the FSP-OP bit (MR13 OP[7]). The values in the registers for the inactive set point will be ignored by the device and may be changed without affecting device operation.

Table 22: Burst Sequence for Read

C4	C3	C2	C1	C0	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	19	20	21	22	23	24	25	26	27	28	29	30	31	32
16-Bit READ Operation																																				
V	**0**	**0**	**0**	**0**	0	1	2	3	4	5	6	7	8	9	A	B	C	D	E	F																
V	**0**	**1**	**0**	**0**	4	5	6	7	8	9	A	B	C	D	E	F	0	1	2	3																
V	**1**	**0**	**0**	**0**	8	9	A	B	C	D	E	F	0	1	2	3	4	5	6	7																
V	**1**	**1**	**0**	**0**	C	D	E	F	0	1	2	3	4	5	6	7	8	9	A	B																
32-Bit READ Operation																																				
0	**0**	**0**	**0**	**0**	0	1	2	3	4	5	6	7	8	9	A	B	C	D	E	F	10	11	12	13	14	15	16	17	18	19	1A	1B	1C	1D	1E	1F
0	**0**	**1**	**0**	**0**	4	5	6	7	8	9	A	B	C	D	E	F	0	1	2	3	14	15	16	17	18	19	1A	1B	1C	1D	1E	1F	10	11	12	13
0	**1**	**0**	**0**	**0**	8	9	A	B	C	D	E	F	0	1	2	3	4	5	6	7	18	19	1A	1B	1C	1D	1E	1F	10	11	12	13	14	15	16	17
0	**1**	**1**	**0**	**0**	C	D	E	F	0	1	2	3	4	5	6	7	8	9	A	B	1C	1D	1E	1F	10	11	12	13	14	15	16	17	18	19	1A	1B
1	**0**	**0**	**0**	**0**	10	11	12	13	14	15	16	17	18	19	1A	1B	1C	1D	1E	1F	0	1	2	3	4	5	6	7	8	9	A	B	C	D	E	F
1	**0**	**1**	**0**	**0**	14	15	16	17	18	19	1A	1B	1C	1D	1E	1F	10	11	12	13	4	5	6	7	8	9	A	B	C	D	E	F	0	1	2	3
1	**1**	**0**	**0**	**0**	18	19	1A	1B	1C	1D	1E	1F	10	11	12	13	14	15	16	17	8	9	A	B	C	D	E	F	0	1	2	3	4	5	6	7
1	**1**	**1**	**0**	**0**	1C	1D	1E	1F	10	11	12	13	14	15	16	17	18	19	1A	1B	C	D	E	F	0	1	2	3	4	5	6	7	8	9	A	B

Notes: 1. C[1:0] are not present on the CA bus; they are implied to be zero.
2. The starting burst address is on 64-bit (4*n*) boundaries.

Table 23: Burst Sequence for Write

C4	C3	C2	C1	C0	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	19	20	21	22	23	24	25	26	27	28	29	30	31	32
16-Bit WRITE Operation																																				
V	**0**	**0**	**0**	**0**	0	1	2	3	4	5	6	7	8	9	A	B	C	D	E	F																
32-Bit WRITE Operation																																				
0	**0**	**0**	**0**	**0**	0	1	2	3	4	5	6	7	8	9	A	B	C	D	E	F	10	11	12	13	14	15	16	17	18	19	1A	1B	1C	1D	1E	1F

Notes: 1. C[1:0] are not present on the CA bus; they are implied to be zero.
2. The starting burst address is on 256-bit (16*n*) boundaries for burst length 16.
3. The starting burst address is on 512-bit (32*n*) boundaries for burst length 32.
4. C[3:2] must be set to 0 for all WRITE operations.

Table 24: MR2 Device Feature 2 (MA[5:0] = 02h)

OP7	OP6	OP5	OP4	OP3	OP2	OP1	OP0
WR Lev	WLS	WL			RL		

Table 25: MR2 Op-Code Bit Definitions

Feature	Type	OP	Definition	Notes
RL READ latency	Write-only	OP[2:0]	RL and *n*RTP for DBI-RD disabled (MR3 OP[6] = 0b) 000b: RL = 6, *n*RTP = 8 (default) 001b: RL = 10, *n*RTP = 8 010b: RL = 14, *n*RTP = 8 011b: RL = 20, *n*RTP = 8 100b: RL = 24, *n*RTP = 10 101b: RL = 28, *n*RTP = 12 110b: RL = 32, *n*RTP = 14 111b: RL = 36, *n*RTP = 16	1, 3, 4
			RL and *n*RTP for DBI-RD enabled (MR3 OP[6] = 1b) 000b: RL = 6, *n*RTP = 8 001b: RL = 12,*n*RTP = 8 010b: RL = 16, *n*RTP = 8 011b: RL = 22, *n*RTP = 8 100b: RL = 28, *n*RTP = 10 101b: RL = 32, *n*RTP = 12 110b: RL = 36, *n*RTP = 14 111b: RL = 40, *n*RTP = 16	

Table 25: MR2 Op-Code Bit Definitions (Continued)

Feature	Type	OP	Definition	Notes
WL WRITE latency	Write-only	OP[5:3]	WL set A (MR2 OP[6] = 0b) 000b: WL = 4 (default) 001b: WL = 6 010b: WL = 8 011b: WL = 10 100b: WL = 12 101b: WL = 14 110b: WL = 16 111b: WL = 18	1, 3, 4
			WL set B (MR2 OP[6] = 1b) 000b: WL = 4 001b: WL = 8 010b: WL = 12 011b: WL = 18 100b: WL = 22 101b: WL = 26 110b: WL = 30 111b: WL = 34	
WLS WRITE latency set	Write-only	OP[6]	0b: Use WL set A (default) 1b: Use WL set B	1, 3, 4
WR Lev Write leveling	Write-only	OP[7]	0b: Disable write leveling (default) 1b: Enable write leveling	2

Notes: 1. See Latency Code Frequency Table for allowable frequency ranges for RL/WL/*n*WR.
2. After an MRW command to set the write leveling enable bit (OP[7] = 1b), the device remains in the MRW state until another MRW command clears the bit (OP[7] = 0b). No other commands are allowed until the write leveling enable bit is cleared.
3. There are two physical registers assigned to each bit of this MR parameter, designated set point 0 and set point 1. Only the registers for the set point determined by the state of the FSP-WR bit (MR13 OP[6]) will be written to with an MRW command this MR address, or read from with an MRR command to this address.
4. There are two physical registers assigned to each bit of this MR parameter, designated set point 0 and set point 1. The device will operate only according to the values stored in the registers for the active set point, that is, the set point determined by the state of the FSP-OP bit (MR13 OP[7]). The values in the registers for the inactive set point will be ignored by the device and may be changed without affecting device operation.
5. *n*RTP is valid for BL16 only. For BL32, the SDRAM will add 8 clocks to the *n*RTP value before starting a precharge.

Table 26: Frequency Ranges for RL, WL, *n*WR, and *n*RTP Settings

READ Latency		WRITE Latency							
No DBI	w/DBI	Set A	Set B	*n*WR	*n*RTP	Lower Frequency Limit (>)	Upper Frequency Limit(≤)	Units	Notes
6	6	4	4	6	8	10	266	MHz	1–6
10	12	6	8	10	8	266	533		
14	16	8	12	16	8	533	800		
20	22	10	18	20	8	800	1066		
24	28	12	22	24	10	1066	1333		
28	32	14	26	30	12	1333	1600		
32	36	16	30	34	14	1600	1866		
36	40	18	34	40	16	1866	2133		

Notes: 1. The device should not be operated at a frequency above the upper frequency limit or below the lower frequency limit shown for each RL, WL, or *n*WR value.
2. DBI for READ operations is enabled in MR3 OP[6]. When MR3 OP[6] = 0, then the "No DBI" column should be used for READ latency. When MR3 OP[6] = 1, then the "w/DBI" column should be used for READ latency.
3. WRITE latency set A and set B are determined by MR2 OP[6]. When MR2 OP[6] = 0, then WRITE latency set A should be used. When MR2 OP[6] = 1, then WRITE latency set B should be used.
4. The programmed value for *n*RTP is the number of clock cycles the device uses to determine the starting point of an internal PRECHARGE operation after a READ burst with AP (auto precharge) enabled . It is determined by RU(^{t}RTP/^{t}CK).
5. The programmed value of *n*WR is the number of clock cycles the device uses to determine the starting point of an internal PRECHARGE operation after a WRITE burst with AP (auto precharge) enabled. It is determined by RU(^{t}WR/^{t}CK).
6. *n*RTP shown in this table is valid for BL16 only. For BL32, the device will add 8 clocks to the *n*RTP value before starting a precharge.

Table 27: MR3 I/O Configuration 1 (MA[5:0] = 03h)

OP7	OP6	OP5	OP4	OP3	OP2	OP1	OP0
DBI-WR	DBI-RD	PDDS			PPRP	WR-PST	PU-CAL

Table 28: MR3 Op-Code Bit Definitions

Feature	Type	OP	Definition	Notes
PU-CAL (Pull-up calibration point)	Write-only	OP[0]	0b: V_{DDQ}/2.5 1b: V_{DDQ}/3 (default)	1–4
WR-PST (WR postamble length)		OP[1]	0b: WR postamble = 0.5 × ^{t}CK (default) 1b: WR postamble = 1.5 × ^{t}CK	2, 3, 5
PPRP (Post-package repair protection)		OP[2]	0b: PPR protection disabled (default) 1b: PPR protection enabled	6
PDDS (Pull-down drive strength)		OP[5:3]	000b: RFU 001b: R_{ZQ}/1 010b: R_{ZQ}/2 011b: R_{ZQ}/3 100b: R_{ZQ}/4 101b: R_{ZQ}/5 110b: R_{ZQ}/6 (default) 111b: Reserved	1, 2, 3
DBI-RD (DBI-read enable)		OP[6]	0b: Disabled (default) 1b: Enabled	2, 3
DBI-WR (DBI-write enable)		OP[7]	0b: Disabled (default) 1b: Enabled	2, 3

Notes: 1. All values are typical. The actual value after calibration will be within the specified tolerance for a given voltage and temperature. Recalibration may be required as voltage and temperature vary.
2. There are two physical registers assigned to each bit of this MR parameter, designated set point 0 and set point 1. Only the registers for the set point determined by the state of the FSP-WR bit (MR13 OP[6]) will be written to with an MRW command to this MR address, or read from with an MRR command to this address.
3. There are two physical registers assigned to each bit of this MR parameter, designated set point 0 and set point 1.The device will operate only according to the values stored in the registers for the active set point, i.e., the set point determined by the state of the FSP-OP bit (MR13 OP[7]). The values in the registers for the inactive set point will be determined by the state of the FSP-OP bit (MR13 OP[7]). The values in the registers for the inactive set point will be ignored by the device, and may be changed without affecting device operation.
4. For dual-channel device, PU-CAL (MR3-OP[0]) must be set the same for both channels on a die. The SDRAM will read the value of only one register (Ch.A or Ch.B), the choice is vendor-specific, so both channels must be set the same.
5. Refer to the supplier data sheet for vender-specific function. 1.5 × ^{t}CK apply > 1.6GHz clock.
6. If MR3 OP[2] is set to 1b, PPR protection mode is enabled. The PPR protection bit is a sticky bit and can only be set to 0b by a power on reset. MR4 OP[4] controls entry to PPR mode. If PPR protection is enabled then the DRAM will not allow writing of 1b to MR4 OP[4].

Table 29: MR4 Device Temperature (MA[5:0] = 04h)

OP7	OP6	OP5	OP4	OP3	OP2	OP1	OP0
TUF	Thermal offset		PPRE	SR abort	Refresh rate		

Table 30: MR4 Op-Code Bit Definitions

Feature	Type	OP	Definition	Notes
Refresh rate	Read-only	OP[2:0]	000b: SDRAM low temperature operating limit exceeded 001b: 4x refresh 010b: 2x refresh 011b: 1x refresh (default) 100b: 0.5x refresh 101b: 0.25x refresh, no derating 110b: 0.25x refresh, with derating 111b: SDRAM high temperature operating limit exceeded	1–4, 7–9
SR abort (Self Refresh Abort)	Write	OP[3]	0b: Disable (default) 1b: Device dependent	9
PPRE (Post-package repair entry/exit)	Write	OP[4]	0b: Exit PPR mode (default) 1b: Enter PPR mode (Reference MR25 OP[7:0] for available PPR resources)	5, 9
Thermal Offset-Controller offset to TCSR	Write	OP[6:5]	00b: No offset, 0~5°C gradient (default) 01b: 5°C offset, 5~10°C gradient 10b: 10°C offset, 10~15°C gradient 11b: Reserved	9
TUF (Temperature update flag)	Read-only	OP7	0b: OP[2:0] No change in OP[2:0] since last MR4 read (default) 1b: Change in OP[2:0] since last MR4 read	6–8

Notes: 1. The refresh rate for each MR4 OP[2:0] setting applies to ^{t}REFI, ^{t}REFIpb, and ^{t}REFW. MR4 OP[2:0] = 011b corresponds to a device temperature of 85°C. Other values require either a longer (2x, 4x) refresh interval at lower temperatures or a shorter (0.5x, 0.25x) refresh interval at higher temperatures. If MR4 OP[2] = 1b, the device temperature is greater than 85°C.
2. At higher temperatures (>85°C), AC timing derating may be required. If derating is required the device will set MR4 OP[2:0] = 110b. See derating timing requirements in the AC Timing section.
3. DRAM vendors may or may not report all of the possible settings over the operating temperature range of the device. Each vendor guarantees that their device will work at any temperature within the range using the refresh interval requested by their device.
4. The device may not operate properly when MR4 OP[2:0] = 000b or 111b.
5. Post-package repair can be entered or exited by writing to MR4 OP[4].
6. When MR4 OP[7] = 1b, the refresh rate reported in MR4 OP[2:0] has changed since the last MR4 read. A mode register read from MR4 will reset MR4 OP[7] to 0b.
7. MR4 OP[7] = 0b at power-up. MR4 OP[2:0] bits are undefined at power-up.
8. See the Temperature Sensor section for information on the recommended frequency of reading MR4.
9. MR4 OP[6:3] can be written in this register. All other bits will be ignored by the device during an MRW command to this register.

Table 31: MR5 Basic Configuration 1 (MA[5:0] = 05h)

OP7	OP6	OP5	OP4	OP3	OP2	OP1	OP0
Manufacturer ID							

Table 32: MR5 Op-Code Bit Definitions

Feature	Type	OP	Definition
Manufacturer ID	Read-only	OP[7:0]	1111 1111b : Micron All others: Reserved

Table 33: MR6 Basic Configuration 2 (MA[5:0] = 06h)

OP7	OP6	OP5	OP4	OP3	OP2	OP1	OP0
Revision ID1							

Note: 1. MR6 is vendor-specific.

Table 34: MR6 Op-Code Bit Definitions

Feature	Type	OP	Definition
Revision ID1	Read-only	OP[7:0]	xxxx xxxxb: Revision ID1

Note: 1. MR6 is vendor-specific.

Table 35: MR7 Basic Configuration 3 (MA[5:0] = 07h)

OP7	OP6	OP5	OP4	OP3	OP2	OP1	OP0
Revision ID2							

Table 36: MR7 Op-Code Bit Definitions

Feature	Type	OP	Definition
Revision ID2	Read-only	OP[7:0]	xxxx xxxxb: Revision ID2

Note: 1. MR7 is vendor-specific.

Table 37: MR8 Basic Configuration 4 (MA[5:0] = 08h)

OP7	OP6	OP5	OP4	OP3	OP2	OP1	OP0
I/O width		Density				Type	

Table 38: MR8 Op-Code Bit Definitions

Feature	Type	OP	Definition
Type	Read-only	OP[1:0]	00b: S16 SDRAM (16*n* prefetch) All others: Reserved
Density	Read-only	OP[5:2]	0000b: 4Gb per die (2Gb per channel) 0001b: 6Gb per die (3Gb per channel) 0010b: 8Gb per die (4Gb per channel) or 4Gb per die (4Gb per channel) 0011b: 12Gb per die (6Gb per channel) or 6Gb per die (6Gb per channel) 0100b: 16Gb per die (8Gb per channel) or 8Gb per die (8Gb per channel) 0101b: 24Gb per die (12Gb per channel) 0110b: 32Gb per die (16Gb per channel) All others: Reserved
I/O width	Read-only	OP[7:6]	00b: x16/channel All others: Reserved

Table 39: MR9 Test Mode (MA[5:0] = 09h)

OP7	OP6	OP5	OP4	OP3	OP2	OP1	OP0
Vendor-specific test mode							

Table 40: MR9 Op-Code Definitions

Feature	Type	OP	Definition
Test mode	Write-only	OP[7:0]	0000000b; Vendor-specific test mode disabled (default)

Table 41: MR10 Calibration (MA[5:0] = 0Ah)

OP7	OP6	OP5	OP4	OP3	OP2	OP1	OP0
RFU							ZQ RESET

Table 42: MR10 Op-Code Bit Definitions

Feature	Type	OP	Definition
ZQ reset	Write-only	OP[0]	0b: Normal operation (default) 1b: ZQ reset

Notes: 1. See AC Timing table for calibration latency and timing.
2. If ZQ is connected to V_{DDQ} through R_{ZQ}, either the ZQ CALIBRATION function or default calibration (via ZQ reset) is supported. If ZQ is connected to V_{SS}, the device operates with default calibration and ZQ CALIBRATION commands are ignored. In both cases, the ZQ connection must not change after power is supplied to the device.

Table 43: MR11 ODT Control (MA[5:0] = 0Bh)

OP7	OP6	OP5	OP4	OP3	OP2	OP1	OP0
RFU	CA ODT			RFU	DQ ODT		

Table 44: MR11 Op-Code Bit Definitions

Feature	Type	OP	Definition
DQ ODT DQ bus receiver on-die termination	Write-only	OP[2:0]	000b: Disable (default) 001b: RZQ/1 010b: RZQ/2 011b: RZQ/3 100b: RZQ/4 101b: RZQ/5 110b: RZQ/6 111b: RFU
CA ODT CA bus receiver on-die termination	Write-only	OP[6:4]	000b: Disable (default) 001b: RZQ/1 010b: RZQ/2 011b: RZQ/3 100b: RZQ/4 101b: RZQ/5 110b: RZQ/6 111b: RFU

Notes: 1. All values are typical. The actual value after calibration will be within the specified tolerance for a given voltage and temperature. Re-calibration may be required as voltage and temperature vary.
2. There are two physical registers assigned to each bit of this MR parameter, designated set point 0 and set point 1. Only the registers for the set point determined by the state of the FSP-WR bit (MR13 OP[6]) will be written to with an MRW command to this MR address, or read from with an MRR command to this address.
3. There are two physical registers assigned to each bit of this MR parameter, designated set point 0 and set point 1. The device will operate only according to the values stored in the registers for the active set point, i.e., the set

point determined by the state of the FSP-OP bit (MR13 OP[7]). The values in the registers for the inactive set point will be ignored by the device and may be changed without affecting device operation.

Table 45: MR12 Register Information (MA[5:0] = 0Ch)

OP7	OP6	OP5	OP4	OP3	OP2	OP1	OP0
RFU	VR_{CA}	$V_{REF(CA)}$					

Table 46: MR12 Op-Code Bit Definitions

Feature	Type	OP	Data	Notes
$V_{REF(CA)}$ $V_{REF(CA)}$ settings	Read/ Write	OP[5:0]	000000b–110010b: See V_{REF} Settings Table All others: Reserved	1–3, 5, 6
VR_{CA} $V_{REF(CA)}$ range	Read/ Write	OP[6]	0b: $V_{REF(CA)}$ range[0] enabled 1b: $V_{REF(CA)}$ range[1] enabled (default)	1, 2, 4, 5, 6

Notes:
1. This register controls the $V_{REF(CA)}$ levels for frequency set point[1:0]. Values from either VR(ca)[0] or VR(ca)[1] may be selected by setting MR12 OP[6] appropriately.
2. A read to MR12 places the contents of OP[7:0] on DQ[7:0]. Any RFU bits and unused DQ will be set to 0. See the MRR Operation section.
3. A write to MR12 OP[5:0] sets the internal $V_{REF(CA)}$ level for FSP[0] when MR13 OP[6] = 0b or sets the internal $V_{REF(CA)}$ level for FSP[1] when MR13 OP[6] = 1b. The time required for $V_{REF(CA)}$ to reach the set level depends on the step size from the current level to the new level. See the $V_{REF(CA)}$ training section.
4. A write to MR12 OP[6] switches the device between two internal $V_{REF(CA)}$ ranges. The range (range[0] or range[1]) must be selected when setting the $V_{REF(CA)}$ register. The value, once set, will be retained until overwritten or until the next power-on or reset event.
5. There are two physical registers assigned to each bit of this MR parameter, designated set point 0 and set point 1. Only the registers for the set point determined by the state of the FSP-WR bit (MR13 OP[6]) will be written to with an MRW command to this MR address, or read from with an MRR command to this address.
6. There are two physical registers assigned to each bit of this MR parameter, designated set point 0 and set point 1. The device will operate only according to the values stored in the registers for the active set point, i.e., the set point determined by the state of the FSP-OP bit (MR13 OP[7]). The values in the registers for the inactive set point will be ignored by the device, and may be changed without affecting device operation.

Table 47: MR13 Register Control (MA[5:0] = 0Dh)

OP[7]	OP[6]	OP[5]	OP[4]	OP[3]	OP[2]	OP[1]	OP[0]
FSP-OP	FSP-WR	DMD	RRO	VRCG	VRO	RPT	CBT

Table 48: MR13 Op-Code Bit Definition

Feature	Type	OP	Definition	Notes
CBT Command bus training	Write-only	OP[0]	0b: Normal operation (default) 1b: Command bus training mode enabled	1
RPT Read preamble training		OP[1]	0b: Disabled (default) 1b: Read preamble training mode enabled	
VRO V_{REF} output		OP[2]	0b: Normal operation (default) 1b: Output the $V_{REF(CA)}$ and $V_{REF(DQ)}$ values on DQ bits	2
VRCG V_{REF} current generator		OP[3]	0b: Normal operation (default) 1b: Fast response (high current) mode	3
RRO Refresh rate option		OP[4]	0b: Disable MR4 OP[2:0] (default) 1b: Enable MR4 OP[2:0]	4, 5
DMD Data mask disable		OP[5]	0b: DATA MASK operation enabled (default) 1b: DATA MASK operation disabled	6
FSP-WR Frequency set point write / read		OP[6]	0b: Frequency set point[0] (default) 1b: Frequency set point[1]	7
FSP-OP Frequency set point operation mode		OP[7]	0b: Frequency set point[0] (default) 1b: Frequency set point[1]	8

Notes: 1. A write to set OP[0] = 1 causes the LPDDR4-SDRAM to enter the Command Bus Training mode. When OP[0] = 1 and CKE goes LOW, commands are ignored and the contents of CA[5:0] are mapped to the DQ bus. CKE must be brought HIGH before doing a MRW to clear this bit (OP[0] = 0) and return to normal operation. See the Command Bus Training section for more information.

2. When set, the device will output the $V_{REF(CA)}$ and $V_{REF(DQ)}$ voltage on DQ pins. Only the "active" frequency set point, as defined by MR13 OP[7], will be output on the DQ pins. This function allows an external test system to measure the internal V_{REF} levels. The DQ pins used for V_{REF} output are vendor-specific.
3. When OP[3] = 1, the V_{REF} circuit uses a high current mode to improve V_{REF} settling time.
4. MR13 OP[4] RRO bit is valid only when MR0 OP[0] = 1. For LPDDR4-SDRAM with MR0 OP[0] = 0, MR4 OP[2:0] bits are not dependent on MR13 OP[4].
5. When OP[4] = 0, only 001b and 010b in MR4 OP[2:0] are disabled. LPDDR4-SDRAM must report 011b instead of 001b or 010b in this case. Controller should follow the refresh mode reported by MR4 OP[2:0], regardless of RRO setting. TCSR function does not depend on RRO setting.
6. When enabled (OP[5] = 0b) data masking is enabled for the device. When disabled (OP[5] = 1b), the device will ignore any mask patterns issued during a MASKED WRITE command. See the Data Mask section for more information.
7. FSP-WR determines which frequency set point registers are accessed with MRW and MRR commands for the following functions such as $V_{REF(CA)}$ setting, $V_{REF(CA)}$ range, $V_{REF(DQ)}$ setting, $V_{REF(DQ)}$ range. For more information, refer to Frequency Set Point section.
8. FSP-OP determines which frequency set point register values are currently used to specify device operation for the following functions such as $V_{REF(CA)}$ setting, $V_{REF(CA)}$ range, $V_{REF(DQ)}$ setting, $V_{REF(DQ)}$ range. For more information, refer to Frequency Set Point section.

Table 49: Mode Register14 (MA[5:0] = 0Eh)

OP[7]	OP[6]	OP[5]	OP[4]	OP[3]	OP[2]	OP[1]	OP[0]
RFU	VR_{DQ}	$V_{REF(DQ)}$					

Table 50: MR14 Op-Code Bit Definition

Feature	Type	OP	Definition	Notes
$V_{REF(DQ)}$ $V_{REF(DQ)}$ setting	Read/Write	OP[5:0]	000000b–110010b: See V_{REF} Settings Table All others: Reserved	1–3, 5, 6
VR_{DQ} $V_{REF(DQ)}$ range		OP[6]	0b: $V_{REF(DQ)}$ range[0] enabled 1b: $V_{REF(DQ)}$ range[1] enabled (default)	1, 2, 4–6

Notes:
1. This register controls the $V_{REF(DQ)}$ levels for frequency set point[1:0]. Values from either VR_{DQ}[0] (vendor defined) or VR_{DQ}[1] (vendor defined) may be selected by setting OP[6] appropriately.
2. A read (MRR) to this register places the contents of OP[7:0] on DQ[7:0]. Any RFU bits and unused DQ shall be set to 0. See the MRR Operation section.
3. A write to OP[5:0] sets the internal $V_{REF(DQ)}$ level for FSP[0] when MR13 OP[6] = 0b, or sets FSP[1] when MR13 OP[6] = 1b. The time required for $V_{REF(DQ)}$ to reach the set level depends on the step size from the current level to the new level. See the $V_{REF(DQ)}$ training section.
4. A write to OP[6] switches the device between two internal $V_{REF(DQ)}$ ranges. The range (range[0] or range[1]) must be selected when setting the $V_{REF(DQ)}$ register. The value, once set, will be retained until overwritten, or until the next power-on or reset event.
5. There are two physical registers assigned to each bit of this MR parameter, designated set point 0 and set point 1. Only the registers for the set point determined by the state of the FSP-WR bit (MR13 OP[6]) will be written to with an MRW command to this MR address, or read from with an MRR command to this address.
6. There are two physical registers assigned to each bit of this MR parameter, designated set point 0 and set point 1. The device will operate only according to the values stored in the registers for the active set point, i.e., the set point determined by the state of the FSP-OP bit (MR13 OP[7]). The values in the registers for the inactive set point will be ignored by the device, and may be changed without affecting device operation.

Table 51: V_{REF} Setting for Range[0] and Range[1]

Function	OP	Range[0] Values		Range[1] Values	
		$V_{REF(CA)}$ (% of V_{DD2})	$V_{REF(DQ)}$ (% of V_{DDQ})	$V_{REF(CA)}$ (% of V_{DD2})	$V_{REF(DQ)}$ (% of V_{DDQ})
V_{REF} Setting for MR12 and MR14	OP[5:0]	000000b: 10.0%	011010b: 20.4%	000000b: 22.0%	011010b: 32.4%
		000001b: 10.4%	011011b: 20.8%	000001b: 22.4%	011011b: 32.8%
		000010b: 10.8%	011100b: 21.2%	000010b: 22.8%	011100b: 33.2%
		000011b: 11.2%	011101b: 21.6%	000011b: 23.2%	011101b: 33.6%
		000100b: 11.6%	011110b: 22.0%	000100b: 23.6%	011110b: 34.0%
		000101b: 12.0%	011111b: 22.4%	000101b: 24.0%	011111b: 34.4%
		000110b: 12.4%	100000b: 22.8%	000110b: 24.4%	100000b: 34.8%
		000111b: 12.8%	100001b: 23.2%	000111b: 24.8%	100001b: 35.2%
		001000b: 13.2%	100010b: 23.6%	001000b: 25.2%	100010b: 35.6%
		001001b: 13.6%	100011b: 24.0%	001001b: 25.6%	100011b: 36.0%
		001010b: 14.0%	100100b: 24.4%	001010b: 26.0%	100100b: 36.4%
		001011b: 14.4%	100101b: 24.8%	001011b: 26.4%	100101b: 36.8%
		001100b: 14.8%	100110b: 25.2%	001100b: 26.8%	100110b: 37.2%
		001101b: 15.2%	100111b: 25.6%	001101b: 27.2% default	100111b: 37.6%
		001110b: 15.6%	101000b: 26.0%	001110b: 27.6%	101000b: 38.0%
		001111b: 16.0%	101001b: 26.4%	001111b: 28.0%	101001b: 38.4%
		010000b: 16.4%	101010b: 26.8%	010000b: 28.4%	101010b: 38.8%
		010001b: 16.8%	101011b: 27.2%	010001b: 28.8%	101011b: 39.2%
		010010b: 17.2%	101100b: 27.6%	010010b: 29.2%	101100b: 39.6%
		010011b: 17.6%	101101b: 28.0%	010011b: 29.6%	101101b: 40.0%
		010100b: 18.0%	101110b: 28.4%	010100b: 30.0%	101110b: 40.4%
		010101b: 18.4%	101111b: 28.8%	010101b: 30.4%	101111b: 40.8%
		010110b: 18.8%	110000b: 29.2%	010110b: 30.8%	110000b: 41.2%
		010111b: 19.2%	110001b: 29.6%	010111b: 31.2%	110001b: 41.6%
		011000b: 19.6%	110010b: 30.0%	011000b: 31.6%	110010b: 42.0%
		011001b: 20.0%	All Others: Reserved	011001b: 32.0%	All Others: Reserved

Notes: 1. These values may be used for MR14 OP[5:0] and MR12 OP[5:0] to set the $V_{REF(CA)}$ or $V_{REF(DQ)}$ levels in the device.
2. The range may be selected in each of the MR14 or MR12 registers by setting OP[6] appropriately.
3. Each of the MR14 or MR12 registers represents either FSP[0] or FSP[1]. Two frequency set points each for CA and DQ are provided to allow for faster switching between terminated and un-terminated operation or between different high-frequency settings, which may use different terminations values.

Table 52: MR15 Register Information (MA[5:0] = 0Fh)

OP[7]	OP[6]	OP[5]	OP[4]	OP[3]	OP[2]	OP[1]	OP[0]
Lower-byte invert register for DQ calibration							

Table 53: MR15 Op-code Bit Definition

Feature	Type	OP	Definition	Notes
Lower-byte invert for DQ calibration	Write-only	OP[7:0]	The following values may be written for any operand OP[7:0] and will be applied to the corresponding DQ locations DQ[7:0] within a byte lane 0b: Do not invert 1b: Invert the DQ calibration patterns in MR32 and MR40 Default value for OP[7:0] = 55h	1–3

Notes: 1. This register will invert the DQ Calibration pattern found in MR32 and MR40 for any single DQ or any combination of DQ. Example: If MR15 OP[7:0] = 00010101b, then the DQ calibration patterns transmitted on DQ[7, 6, 5, 3, 1] will not be inverted, but the DQ calibration patterns transmitted on DQ[4, 2, 0] will be inverted.
2. DM[0] is not inverted and always transmits the "true" data contained in MR32 and MR40.
3. No data bus inversion (DBI) function is enacted during DQ read calibration, even if DBI is enabled in MR3-OP[6].

Table 54: MR15 Invert Register Pin Mapping

PIN	DQ0	DQ1	DQ2	DQ3	DMIO	DQ4	DQ5	DQ6	DQ7
MR15	OP0	OP1	OP2	OP3	No invert	OP4	OP5	OP6	OP7

Table 55: MR16 PASR Bank Mask (MA[5:0] = 010h)

OP7	OP6	OP5	OP4	OP3	OP2	OP1	OP0
PASR bank mask							

Table 56: MR16 Op-Code Bit Definitions

Feature	Type	OP	Definition
Bank[7:0] mask	Write-only	OP[7:0]	0b: Bank refresh enabled (default) 1b: Bank refresh disabled

$OP[_n]$	Bank Mask	8-Bank SDRAM
0	xxxxxxx1	Bank 0
1	xxxxxx1x	Bank 1
2	xxxxx1xx	Bank 2
3	xxxx1xxx	Bank 3
4	xxx1xxxx	Bank 4
5	xx1xxxxx	Bank 5
6	x1xxxxxx	Bank 6
7	1xxxxxxx	Bank 7

Notes: 1. When a mask bit is asserted (OP[*n*] = 1), refresh to that bank is disabled.
2. PASR bank masking is on a per-channel basis; the two channels on the die may have different bank masking.

Table 57: MR17 PASR Segment Mask (MA[5:0] = 11h)

OP7	OP6	OP5	OP4	OP3	OP2	OP1	OP0
PASR segment mask							

Table 58: MR17 PASR Segment Mask Definitions

Feature	Type	OP	Definition
Segment[7:0] mask	Write-only	OP[7:0]	0b: Segment refresh enabled (default) 1b: Segment refresh disabled

Table 59: MR17 PASR Segment Mask

Segment	OP	Segment Mask	Density (per channel)						
			2Gb	3Gb	4Gb	6Gb	8Gb	12Gb	16Gb
			R[13:11]	R[14:12]	R[14:12]	R[15:13]	R[15:13]	TBD	TBD
0	0	XXXXXXX1	000b						
1	1	XXXXXX1X	001b						
2	2	XXXXX1XX	010b						
3	3	XXXX1XXX	011b						
4	4	XXX1XXXX	100b						
5	5	XX1XXXXX	101b						
6	6	X1XXXXXX	110b	Not allowed	110b	Not allowed	110b	Not allowed	110b
7	7	1XXXXXXX	111b		111b		111b		111b

Notes: 1. This table indicates the range of row addresses in each masked segment. "X" is “Don’t Care” for a particular segment.
2. PASR segment-masking is on a per-channel basis. The two channels on the die may have different segment masking.
3. For 3Gb, 6Gb, and 12Gb density per channel, OP[7:6] must always be LOW (= 00b).

Table 60: MR18 Register Information (MA[5:0]=12h)

OP7	OP6	OP5	OP4	OP3	OP2	OP1	OP0
DQS oscillator count - LSB							

Table 61: MR18 LSB DQS Oscillator Count

Function	Type	OP	Definition
DQS oscillator count (WR training DQS oscillator)	Read-only	OP[7:0]	0h–FFh LSB DRAM DQS oscillator count

Notes: 1. MR18 reports the LSB bits of the DRAM DQS oscillator count. The DRAM DQS oscillator count value is used to train DQS to the DQ data valid window. The value reported by the DRAM in this mode register can be used by the memory controller to periodically adjust the phase of DQS relative to DQ.
2. Both MR18 and MR19 must be read (MRR) and combined to get the value of the DQS oscillator count.
3. The value in this register is reset each time an MPC command is issued to start in the DQS oscillator counter.

Table 62: MR19 Register Information (MA[5:0] = 13h)

OP7	OP6	OP5	OP4	OP3	OP2	OP1	OP0
DQS oscillator count – MSB							

Table 63: MR19 DQS Oscillator Count

Function	Type	OP	Definition
DQS oscillator count – MSB (WR training DQS oscillator)	Read-only	OP[7:0]	0h–FFh MSB DRAM DQS oscillator count

Notes: 1. MR19 reports the MSB bits of the DRAM DQS oscillator count. The DRAM DQS oscillator count value is used to train DQS to the DQ data valid window. The value reported by the DRAM in this mode register can be used by the memory controller to periodically adjust the phase of DQS relative to DQ.
2. Both MR18 and MR19 must be read (MRR) and combined to get the value of the DQS oscillator count.
3. A new MPC[START DQS OSCILLATOR]] should be issued to reset the contents of MR18/MR19.

Table 64: MR20 Register Information (MA[5:0] = 14h)

OP7	OP6	OP5	OP4	OP3	OP2	OP1	OP0
Upper-byte invert register for DQ calibration							

Table 65: MR20 Register Information

Function	Type	OP	Definition
Upper-byte invert for DQ calibration	Write-only	OP[7:0]	The following values may be written for any operand OP[7:0] and will be applied to the corresponding DQ locations DQ[15:8] within a byte lane 0b: Do not invert 1b: Invert the DQ calibration patterns in MR32 and MR40 Default value for OP[7:0] = 55h

Notes: 1. This register will invert the DQ calibration pattern found in MR32 and MR40 for any single DQ or any combination of DQ. For example, if MR20 OP[7:0] = 00010101b, the DQ calibration patterns transmitted on DQ[15, 14, 13, 11, 9] will not be inverted, but the DQ calibration patterns transmitted on DQ[12, 10, 8] will be inverted.
2. DM[1] is not inverted and always transmits the true data contained in MR32 and MR40.
3. No data bus inversion (DBI) function is enacted during DQ read calibration, even if DBI is enabled in MR3 OP[6].

Table 66: MR20 Invert Register Pin Mapping

Pin	DQ8	DQ9	DQ10	DQ11	DMI1	DQ12	DQ13	DQ14	DQ15
MR20	OP0	OP1	OP2	OP3	No invert	OP4	OP5	OP6	OP7

Table 67: MR21 Register Information (MA[5:0] = 15h)

OP7	OP6	OP5	OP4	OP3	OP2	OP1	OP0
RFU							

Table 68: MR22 Register Information (MA[5:0] = 16h)

OP7	OP6	OP5	OP4	OP3	OP2	OP1	OP0
RFU		ODTD-CA	ODTE-CS	ODTE-CK	SOC ODT		

Table 69: MR22 Register Information

Function	Type	OP	Data	Notes
SOC ODT (controller ODT value for V_{OH} calibration)	Write-only	OP[2:0]	000b: Disable (default) 001b: $R_{ZQ}/1$ 010b: $R_{ZQ}/2$ 011b: $R_{ZQ}/3$ 100b: $R_{ZQ}/4$ 101b: $R_{ZQ}/5$ 110b: $R_{ZQ}/6$ 111b: RFU	1, 2, 3
ODTE-CK (CK ODT enabled for non-terminating rank)	Write-only	OP[3]	0b: ODT-CK override disabled (default) 1b: ODT-CK override enabled	2, 3, 4, 6, 8
ODTE-CS (CS ODT enabled for non-terminating rank)	Write-only	OP[4]	0b: ODT-CS override disabled (default) 1b: ODT-CS override enabled	2, 3, 5, 6, 8
ODTD-CA (CA ODT termination disable)	Write-only	OP[5]	0b: CA ODT obeys ODT_CA bond pad (default) 1b: CA ODT disabled	2, 3, 6, 7, 8

Notes: 1. All values are typical.
2. There are two physical registers assigned to each bit of this MR parameter: designated set point 0 and set point 1. Only the registers for the set point determined by the state of the FSP-WR bit (MR13 OP[6]) will be written to with an MRW command or read from with an MRR command to this address.
3. There are two physical registers assigned to each bit of this MR parameter: designated set point 0 and set point 1. The device will operate only according to the values stored in the registers for the active set point determined by the state of the FSP-OP bit (MR13 OP[7]). The values in the registers for the inactive set point will be ignored by the device and may be changed without affecting device operation.
4. When OP[3] = 1 the CK signals will be terminated to the value set by MR11 OP[6:4] regardless of the state of the ODT_CA bond pad. This overrides the ODT_CA bond pad for configurations where CA is shared by two or more devices but CK is not, enabling CK to terminate on all devices.
5. When OP[4] = 1 the CS signal will be terminated to the value set by MR11 OP[6:4] regardless of the state of the ODT_CA bond pad. This overrides the ODT_CA bond pad for configurations where CA is shared by two or more devices but CS is not, enabling CS to terminate on all devices.
6. For system configurations where the CK, CS, and CA signals are shared between packages, the package design should provide for the ODT_CA ball to be bonded on the system board outside of the memory package. This provides the necessary control of the ODT function for all die with shared command bus signals.
7. When OP[5] = 0, CA[5:0] will terminate when the ODT_CA bond pad is HIGH and MR11 OP[6:4] is valid and disable termination when ODT_CA is LOW or MR11 OP[6:4] is disabled. When OP[5] = 1, termination for CA[5:0] is disabled regardless of the state of the ODT_CA bond pad or MR11 OP[6:4].
8. To ensure proper operation in a multi-rank configuration, when CA, CK or CS ODT is enabled via MR11 OP[6:4] and also via MR22 or ODT_CA pad setting, the rank providing ODT will continue to terminate the command bus in all DRAM states including Active, Self-refresh, Self-refresh Power-down, Active Power-down and Precharge Power-down.

Table 70: MR23 Register Information (MA[5:0] = 17h)

OP7	OP6	OP5	OP4	OP3	OP2	OP1	OP0
DQS interval timer run-time setting							

Table 71: MR23 Register Information

Function	Type	OP	Data
DQS interval timer run-time	Write-only	OP[7:0]	00000000b: Disabled (default) 00000001b: DQS timer stops automatically at the 16th clock after timer start 00000010b: DQS timer stops automatically at the 32nd clock after timer start 00000011b: DQS timer stops automatically at the 48th clock after timer start 00000100b: DQS timer stops automatically at the 64th clock after timer start --------- Through --------- 00111111b: DQS timer stops automatically at the (63 × 16)th clock after timer start 01XXXXXXb: DQS timer stops automatically at the 2048th clock after timer start 10XXXXXXb: DQS timer stops automatically at the 4096th clock after timer start 11XXXXXXb: DQS timer stops automatically at the 8192nd clock after timer start

Notes: 1. MPC command with OP[6:0] = 1001101b (stop DQS Interval Oscillator) stops the DQS interval timer in the case of MR23 OP[7:0] = 00000000b.
2. MPC command with OP[6:0] = 1001101b (stop DQS Interval Oscillator) is illegal with valid nonzero values in MR23 OP[7:0].

Table 72: MR24 Register Information (MA[5:0] = 18h)

OP7	OP6	OP5	OP4	OP3	OP2	OP1	OP0
TRR mode	TRR mode BAn			Unlimited MAC	MAC value		

Table 73: MR24 Register Information

Function	Type	OP	Data	Notes
MAC value	Read	OP[2:0]	000b: Unknown (OP[3] = 0) or Unlimited (OP[3] = 1) 001b: 700K 010b: 600K 011b: 500K 100b: 400K 101b: 300K 110b: 200K 111b: Reserved	1
Unlimited MAC	Read	OP[3]	0b: OP[2:0] defines the MAC value 1b: Unlimited MAC value	2

Table 73: MR24 Register Information (Continued)

Function	Type	OP	Data	Notes
TRR mode BAn	Write	OP[6:4]	000b: Bank 0 001b: Bank 1 010b: Bank 2 011b: Bank 3 100b: Bank 4 101b: Bank 5 110b: Bank 6 111b: Bank 7	
TRR mode	Write	OP[7]	0b: Disabled (default) 1b: Enabled	

Notes: 1. OP[2:0]=000b Unknown means that the device is not tested for ^{t}MAC and pass/fail values are unknown. OP[2:0]=000b Unlimited means that there is no restriction on the number of activates between refresh windows. However, specific attempts to by-pass TRR may result in data disturb.
2. When OP[3]=1b, MR24 OP[2:0] set to 000b.

Table 74: MR25 Register Information (MA[5:0] = 19h)

OP7	OP6	OP5	OP4	OP3	OP2	OP1	OP0
Bank 7	Bank 6	Bank 5	Bank 4	Bank 3	Bank 2	Bank 1	Bank 0

Table 75: MR25 Register Information

Function	Type	OP	Data
PPR resources	Read-only	OP[7:0]	0b: PPR resource is not available 1b: PPR resource is available

Note: 1. When OP[n] = 0, there is no PPR resource available for that bank. When OP[n] = 1, there is a PPR resource available for that bank, and PPR can be initiated by the controller.

Table 76: MR26:31 Register Information (MA[5:0] = 1Ah–1Fh)

OP7	OP6	OP5	OP4	OP3	OP2	OP1	OP0
Reserved for future use							

Table 77: MR32 Register Information (MA[5:0] = 20h)

OP7	OP6	OP5	OP4	OP3	OP2	OP1	OP0
DQ calibration pattern A (default = 5Ah)							

Table 78: MR32 Register Information

Function	Type	OP	Data	Notes
Return DQ calibration pattern MR32 + MR40	Write-only	OP[7:0]	Xb: An MPC command issued with OP[6:0] = 1000011b causes the device to return the DQ calibration pattern contained in this register and (followed by) the contents of MR40. A default pattern 5Ah is loaded at power-up or reset, or the pattern may be overwritten with a MRW to this register. The contents of MR15 and MR20 will invert the MR32/MR40 data pattern for a given DQ (see MR15/MR20 for more information).	1, 2, 3

Notes: 1. The patterns contained in MR32 and MR40 are transmitted on DQ[15:0] and DMI[1:0] when DQ read calibration is initiated via an MPC command. The pattern is transmitted serially on each data lane and organized little endian such that the low-order bit in a byte is transmitted first. If the data pattern is 27H, the first bit transmitted is a 1 followed by 1, 1, 0, 0, 1, 0, and 0. The bit stream will be 00100111.
2. MR15 and MR20 may be used to invert the MR32/MR40 data pattern on the DQ pins. See MR15 and MR20 for more information. Data is never inverted on the DMI[1:0] pins.
3. The data pattern is not transmitted on the DMI[1:0] pins if DBI-RD is disabled via MR3 OP[6].
4. No data bus inversion (DBI) function is enacted during DQ read calibration, even if DBI is enabled in MR3 OP[6].

Table 79: MR33:39 Register Information (MA[5:0] = 21h–27h)

OP7	OP6	OP5	OP4	OP3	OP2	OP1	OP0
Do not use							

Table 80: MR40 Register Information (MA[5:0] = 28h)

OP7	OP6	OP5	OP4	OP3	OP2	OP1	OP0
DQ calibration pattern B (default = 3Ch)							

Table 81: MR40 Register Information

Function	Type	OP	Data	Notes
Return DQ calibration pattern MR32 + MR40	Write-only	OP[7:0]	Xb: A default pattern 3Ch is loaded at power-up or reset, or the pattern may be overwritten with a MRW to this register. See MR32 for more information.	1, 2, 3

Notes: 1. The pattern contained in MR40 is concatenated to the end of MR32 and transmitted on DQ[15:0] and DMI[1:0] when DQ read calibration is initiated via an MPC command. The pattern is transmitted serially on each data lane and organized little endian such that the low-order bit in a byte is transmitted first. If the data pattern in MR40 is 27H, the first bit transmitted will be a 1, followed by 1, 1, 0, 0, 1, 0, and 0. The bit stream will be 00100111.
2. MR15 and MR20 may be used to invert the MR32/MR40 data patterns on the DQ pins. See MR15 and MR20 for more information. Data is never inverted on the DMI[1:0] pins.
3. The data pattern is not transmitted on the DMI[1:0] pins if DBI-RD is disabled via MR3 OP[6].
4. No data bus inversion (DBI) function is enacted during DQ read calibration, even if DBI is enabled in MR3 OP[6].

Table 82: MR41:47 Register Information (MA[5:0] = 29h–2Fh)

OP7	OP6	OP5	OP4	OP3	OP2	OP1	OP0
Do not use							

Table 83: MR48:63 Register Information (MA[5:0] = 30h–3Fh)

OP7	OP6	OP5	OP4	OP3	OP2	OP1	OP0
Reserved for future use							

Revision History

Rev. G - 11/24

- Updated IDD tables

Rev. F - 4/24

- Added DT package and Part Number List

Rev. E – 03/2020

- Updated MR24 table notes

Rev. D – 7/18

Rev. C – 5/17

- Added Important Notes and Warnings section for further clarification aligning to industry standards
- Removed "preliminary" designation from the 200-ball WFBGA (10mm x 14.5mm, Ø0.35 SMD package

Rev. B – 1 /17

- Production status release
- Added package (Package Code: DS)
- Added Functional Block Diagram in Functional Description
- Updated ^{t}DSS/^{t}DSH timing definition
- Added new Burst Read operation timing with Per Bank Refresh

Rev. A – 9 /16

- Preliminary status release based on 200b_z00n_auto_lpddr4.pdf – Rev. B 6/ 16 EN

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This data sheet contains minimum and maximum limits specified over the power supply and temperature range set forth herein.
Although considered final, these specifications are subject to change, as further product development and data characterization sometimes occur.